The History of Silicon Detectors for Particle and X-ray Physics

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The Very Early Days of Solid State Detectors

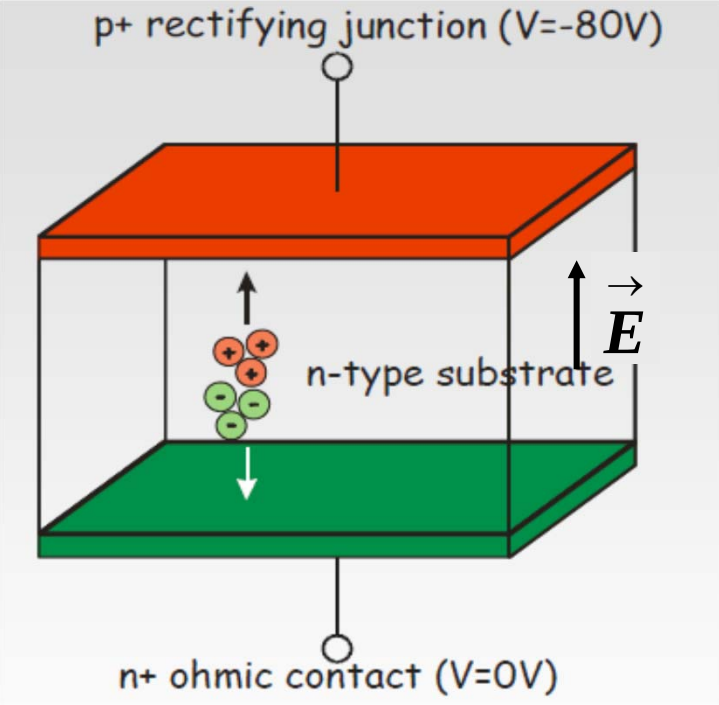
Idea of solid state ionization chamber and first successful realisations:

- 1943: P.J. von Heerden, Utrecht (AgCl)
- 1949: K.G. McKay, Bell (Ge – pn junction)
- 1955 – 1965: Si mono-crystals available

→ surface barrier detectors at several labs. Oak Ridge, Chalk River, CEA, ... main motivation nuclear particle spectrometers

- 1961: G. Dearnaley, Harwell :first segmented detector a pixel detector !
- 1970: first strip detectors – Argonne, Fermilab, Karlsruhe, Southampton; for nuclear physics and nuclear medicine
- 1970: W.S. Boyle and G.E. Smith, Bell CCD

Several companies in the US and Europe for detector fabrication (> 7 in 1975)



typical values for Si:

- voltage: 50 – 500 V
- thickness: 0.05 – 1 mm
- signal: 1e/h-pair/3.6 eV
  -> mip 25000 charges/0.3 mm
- collection time: 5-50 ns
- diffusion: few μm
- sensitive to light < ~1 μm, x-rays 0.2-~20keV,charged part.

The Very Early Days

Si-detectors can also be used to detect minimum ionizing particles !

(J.E.Bateman, NIM 71(1969)256)

- surface barrier detector
- area: 2 cm^2
- thickness: 500 μm
- resistivity: 8 $k\Omega \cdot cm$
- voltage: 400 V
- noise: ~ 4000 e (rms)

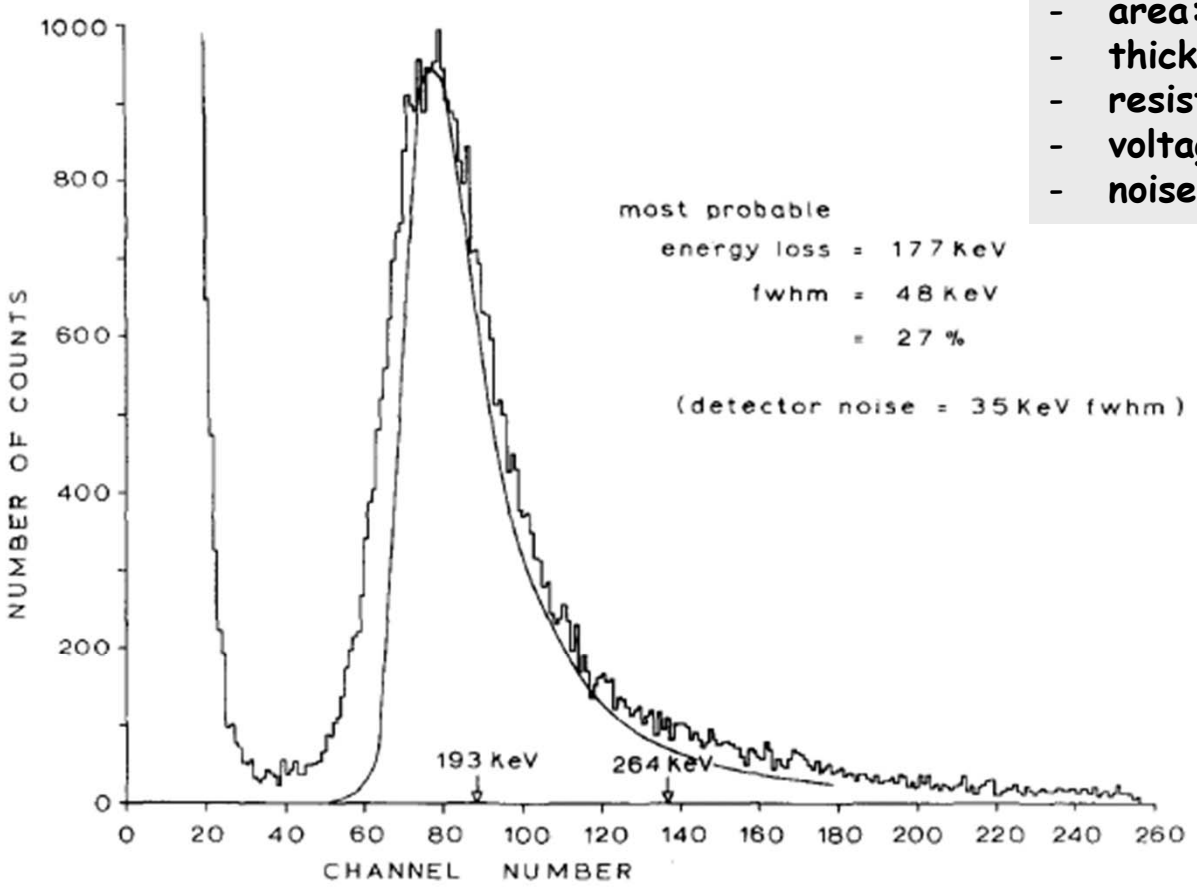


Fig. 4. Energy distribution produced in C56 by electrons of energy 150 MeV (momentum resolution ≈ 2%). The solid curve is given by Landau's theory.

Early Realization of Double Sided Strip Detector

S.M.Gruner BSC-thesis (1972):

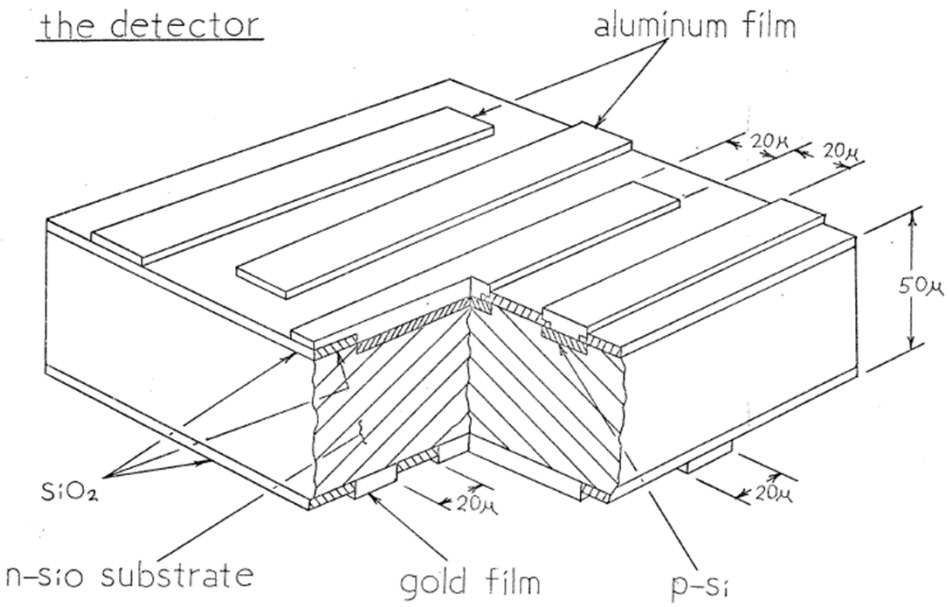
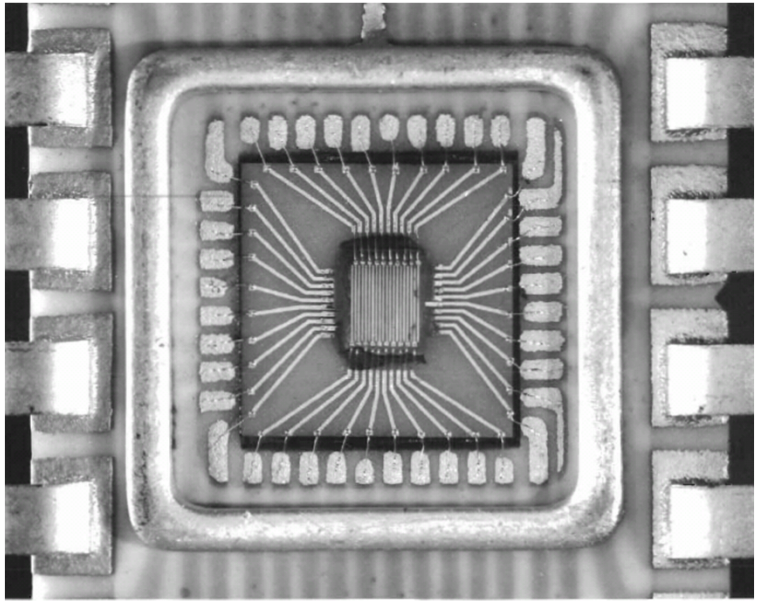


figure 3



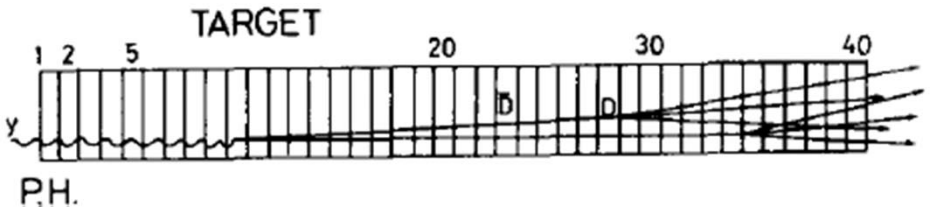
Conclusion

The feasibility of initiating the fabrication of a large area integrated circuit semiconductor detector following our basic design has been demonstrated both conceptually and experimentally. The initial fabrication of a small test device has shown that the construction problems can be overcome. Further, testing of the small device has yielded attractive resolution in space and time (20 microns; 10 nano-seconds) and has done so with a signal to noise ratio which allows digital logic handling.

- (.6×.6) mm²×50 µm n-type Si
- B-diffused (+Al): p^+n-junction
- Au strips: np-junction
- test with ^{90}Sr source + amplifier + scope

The Very Early Days of Si Detectors in hep

Segmented active target 1973 (G. Bellini et al. , NA-1 at CERN Coherent production π +Si → 3π + Si; and later for charm)



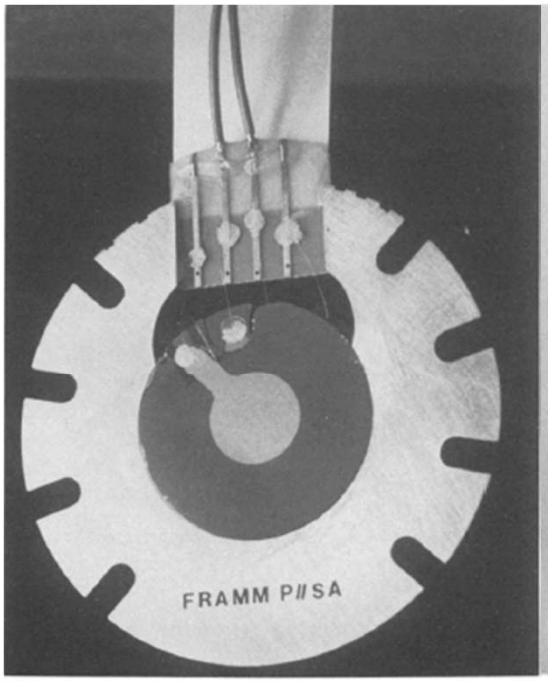


Fig. 3. Silicon disk.

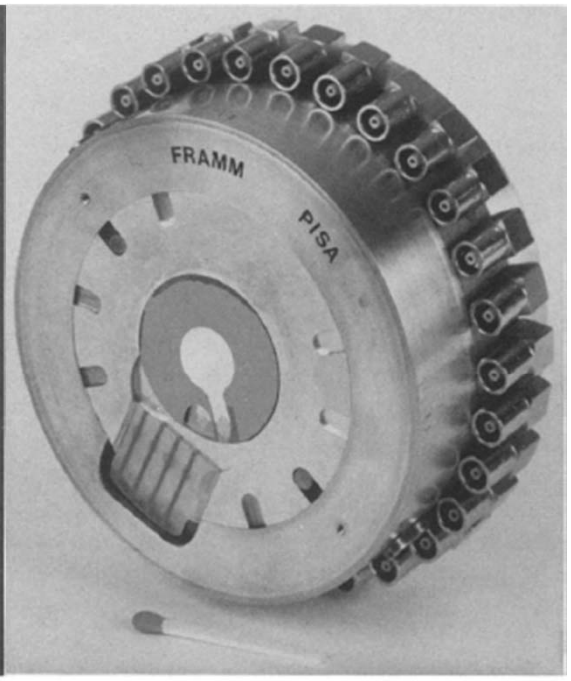


Fig. 5. Assembly of the whole telescope.

Surface barriers: a "mystic" art

- reliability not guaranteed
- but successful experiments and great potential

→ limited use

This changed in 1974 with

- discovery of J/ψ
- paper by Gaillard, Lee und Rosner on charmed particles
- discovery of charm (1975) (lifetime $c\tau$ ~ 100 μm)
- discovery of τ-lepton
- discovery of beauty

→ Hunt for high position resolution electronic detectors

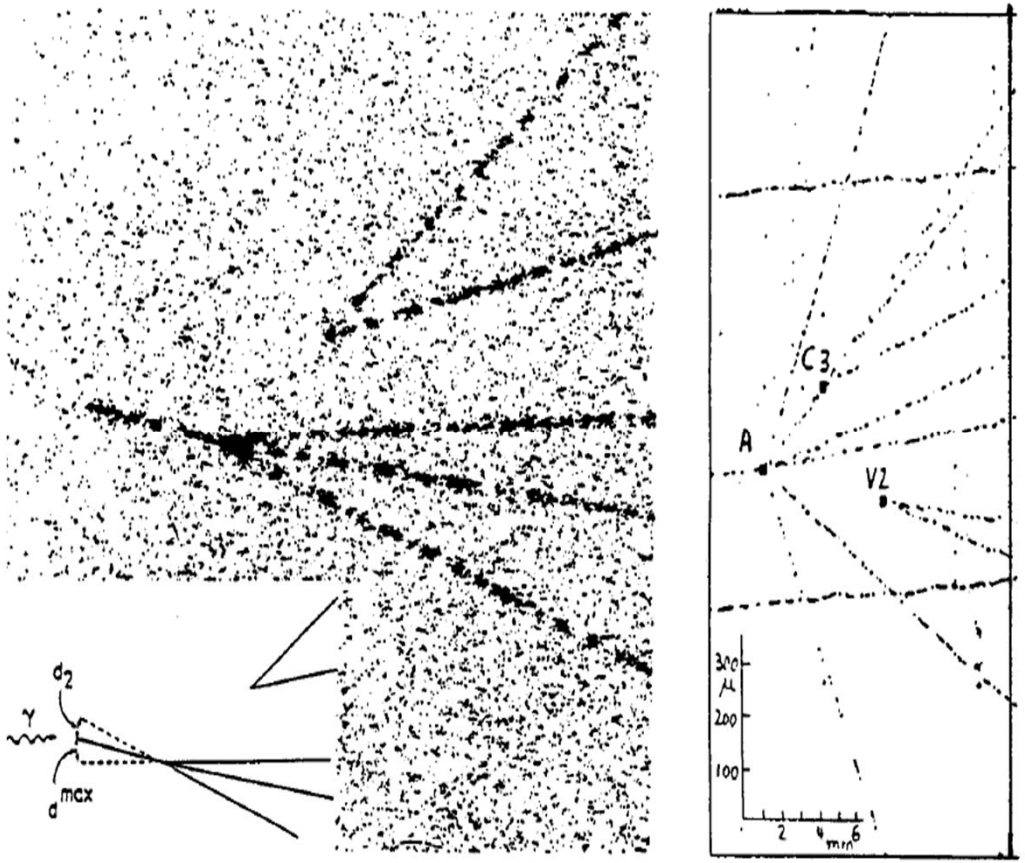
(a friendly competition between gaseous and solid state approach)

The Hunt for High Resolution Electronic Detectors

But there are **3 reasons** why the development of high position resolution Si-detectors took off in the late seventies:

- discovery of short-lived particles; lifetime $c\tau \sim 100\ \mu m$ defines required resolution
- highly developed Si-technology for electronics (crystals + the planar process)
- development of miniaturized electronics (thick film hybrids → VLSI) generally available

→ Several hep groups started to learn the art of silicon sensors and μ-electronics (in close collaboration with industry)

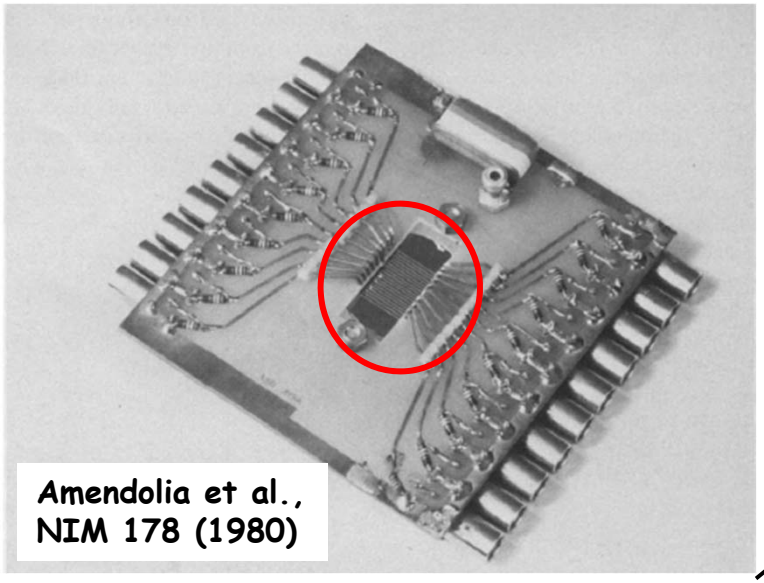


high resolution bubble chambers: SLAC - CERN (production charm-anticharm)

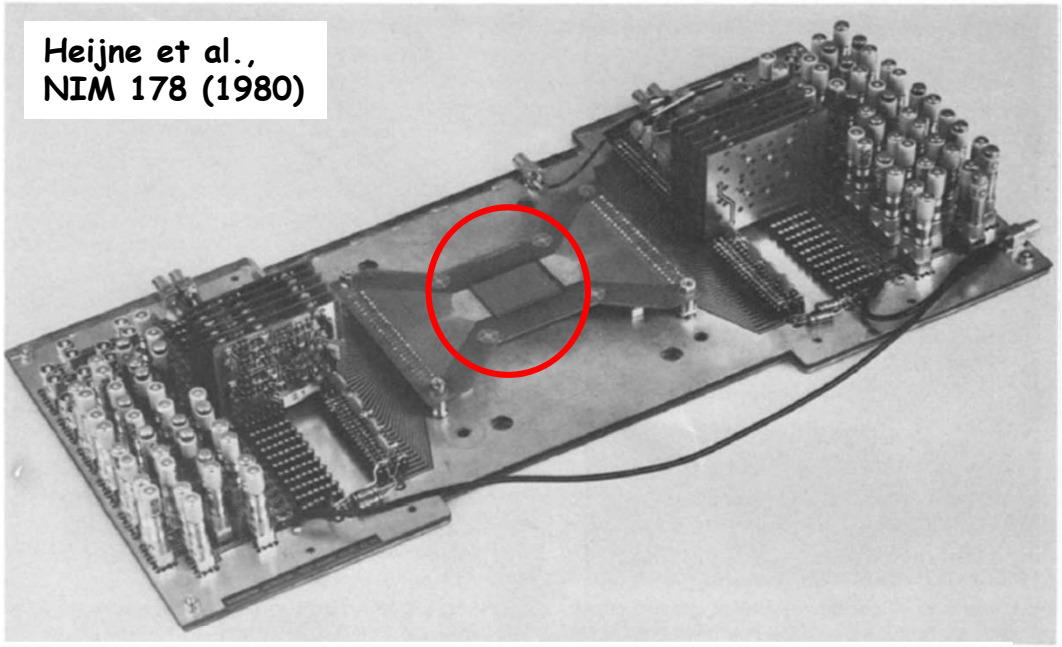
The Early Days of Si Strip Detectors in hep

Still surface barrier technology:

PISA group (Amendolia et al. 1980) →
Si-strip sensor with 600 μm pitch



Amendolia et al.,
NIM 178 (1980)



Heijne et al.,
NIM 178 (1980)

CERN group (Hyams et al. 1980)
Si-strip sensor with 300 μm pitch

- demonstrate vertex reconstruction (within the NA-11 experiment)
- demonstrate capacitive charge division (thanks to broken channels)

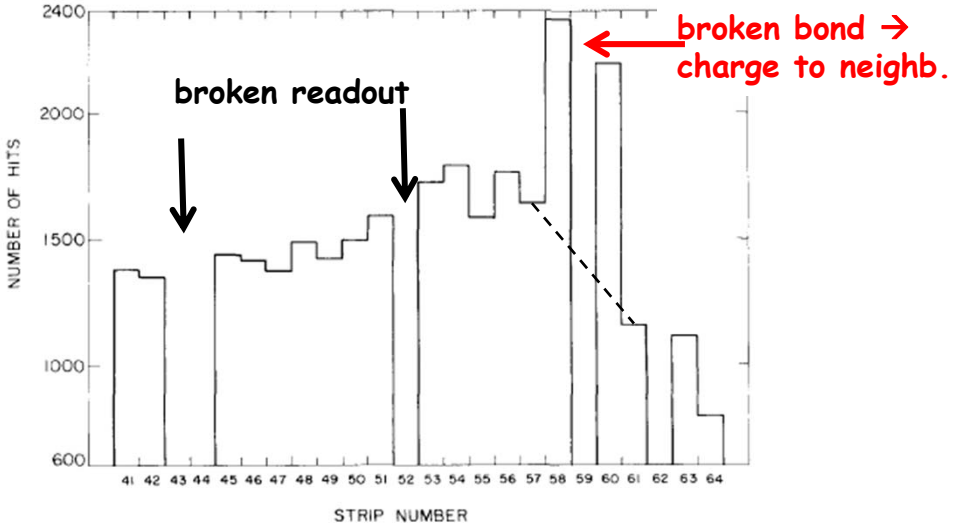
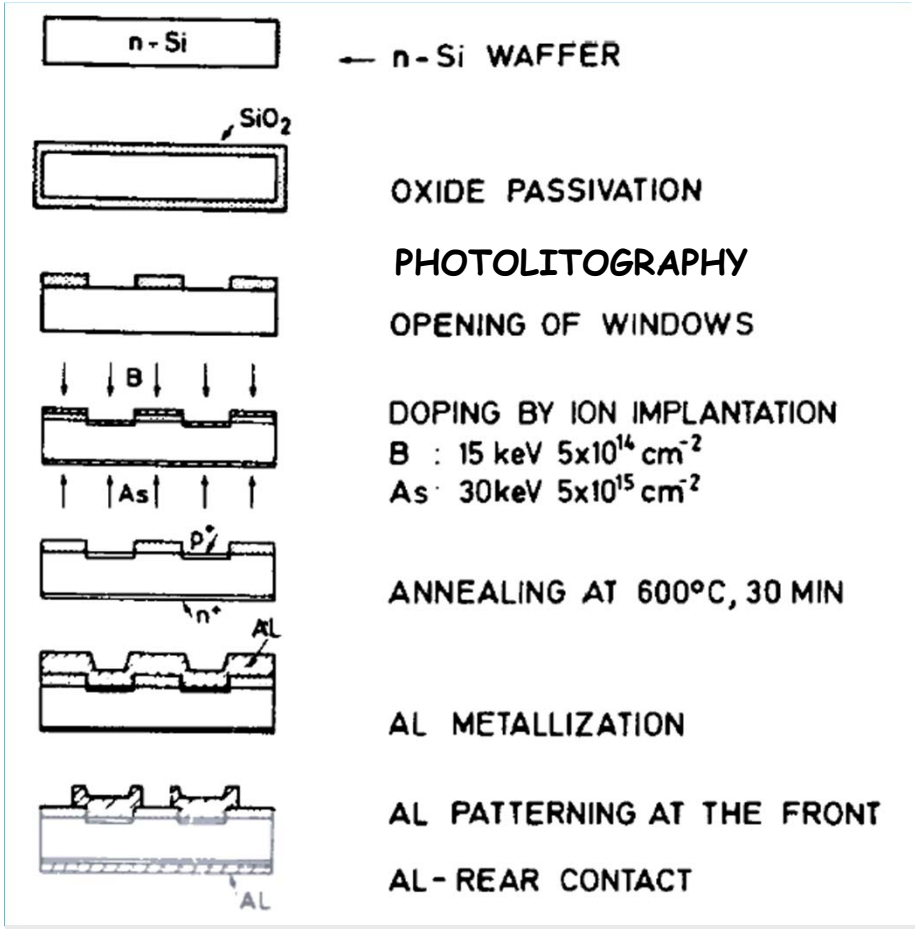


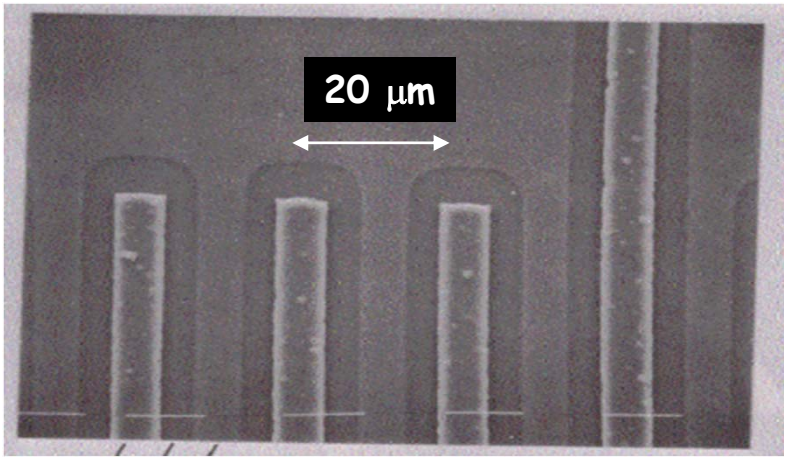
Fig. 10. Hit distribution over 24 strips in the 10 GeV beam. Amplifiers on strips 43, 44, 52 and 62 were not working. Strip 59 has a broken contact, but its signals are collected on either 58 or 60.

Transfer of the Planar Process to Detector Fabrication

Kemmer 1979, TU-München, transferred the highly developed Si-technology for electronics to detector fabrication
+ industry (P. Burger – Enertec/Canberra)



J. Kemmer, NIM 169(1980)499 and NIM 226(1984)89



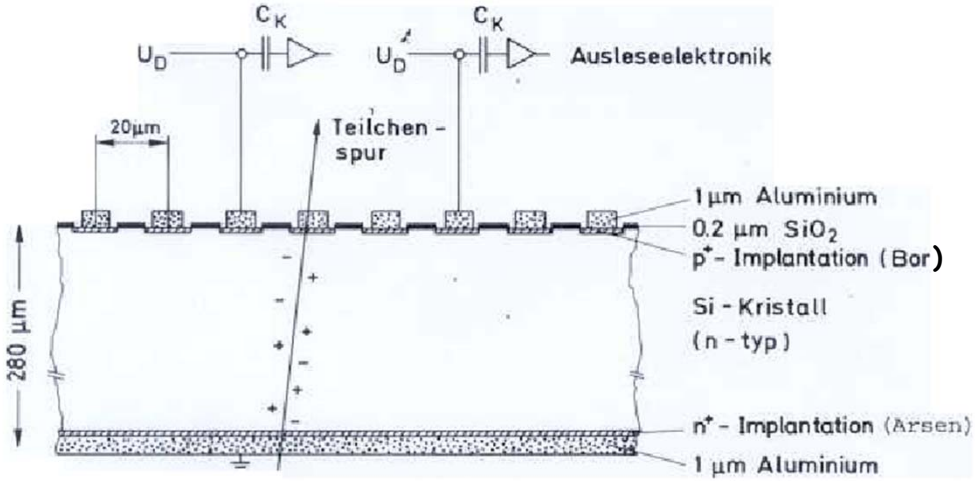
Getting Organized

1983: 3rd European Symposium on Semiconductor Detectors at Munich

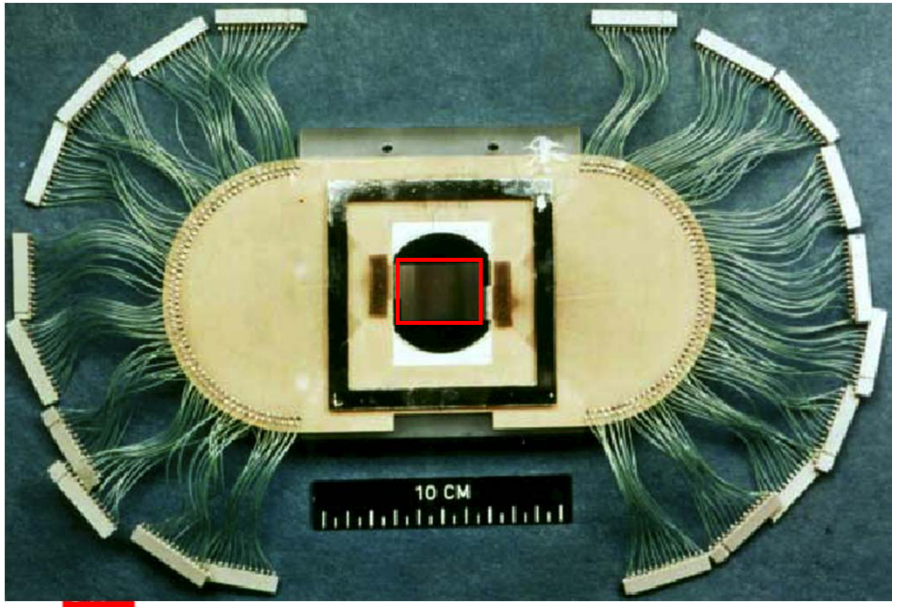
Si-strip Detector Telescope in CERN NA11 Experiment

NA-11/32 experiment:

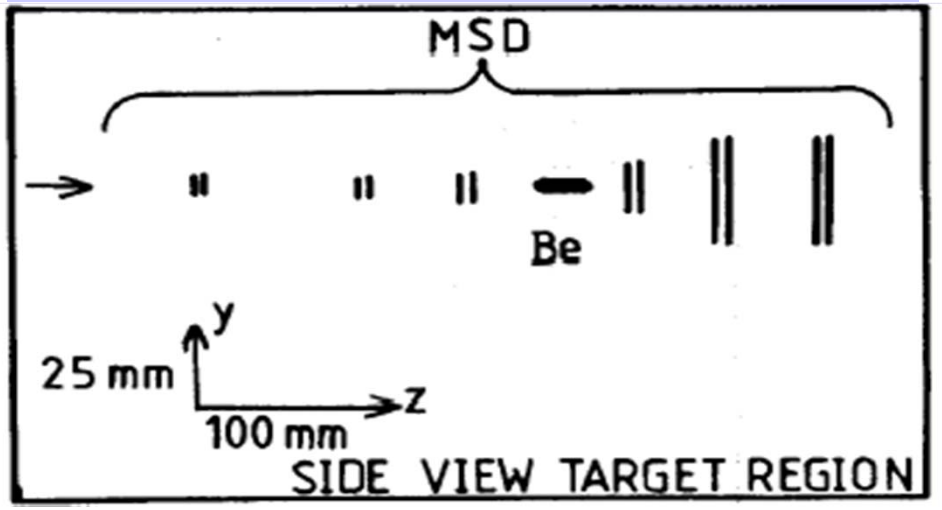
- spectrometer for the study of hadronic reactions eg πBe->charm+X
- **1981**: 6 planes Si-strip detectors
  - * 24x36mm^2, 1200 strips/sensor
  - * strip pitch 20 μm, 280 μm thick
  - * 60 μm readout → σ =5.4 μm
  - * 120 μm readout → σ=7.8 μm
  - * total <2000 channels
  - * 100% efficiency



B.Hyams et al., NIM 205(1983)99



NA-11 target region



Results from the NA11 Experiment

NA-11/32: Charm physics results

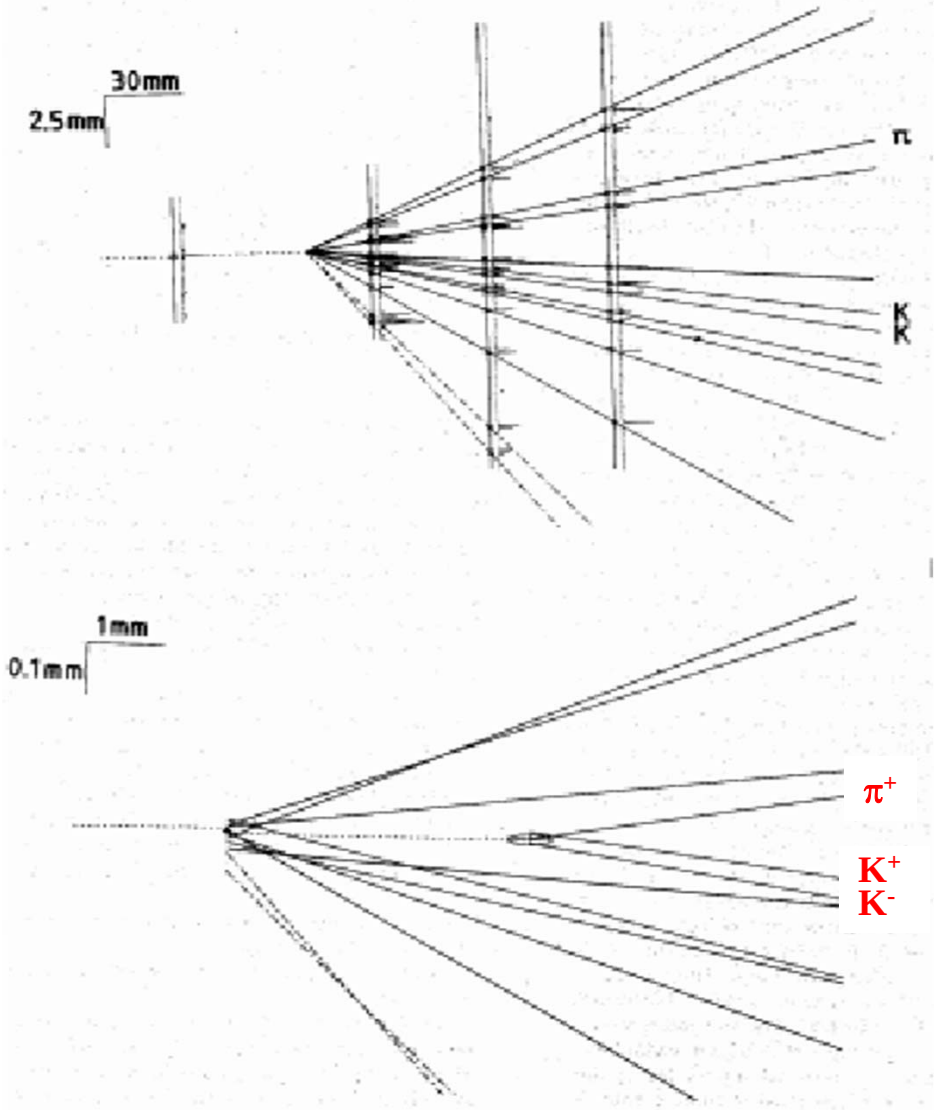
- lifetimes D^+, D^0, D_S, Λ_c, ...
- observation and mass of D_S,
- hadronic production of charm particles (QCD)

Impact of NA11/32:

- demonstrated excellent performance of Si-strip detectors
- demonstrated excellent performance of pixel detectors
  (→ CCDs have been added in NA32)
- testing ground for new ideas and concepts (→ Si drift ch.)
- **learning- + communication-environment for junior and senior Si-experts**

(R.Horisberger, D.Dorfan, S.Parker, U.Kötz, V.Lüth, E.Gatti, P.Rehak + many more)

Observation of $D_S \rightarrow \phi\,\pi$

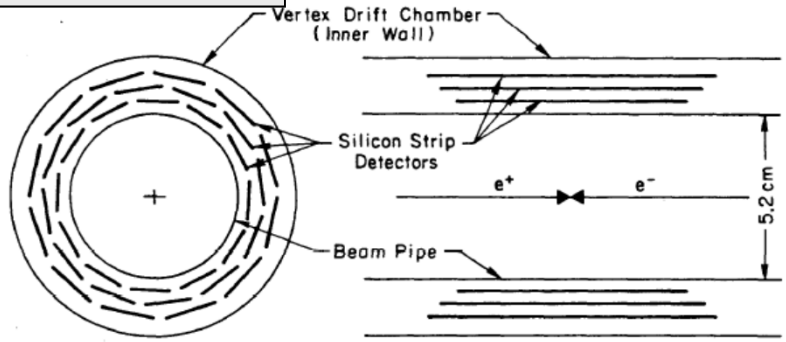


Si Vertex Detector for e^+e^-: SVD at Mark-II at SLC

Parallel to Si-detectors → development of VLSI readout chips
(**CAMEX**: G.Lutz et al., MPI; **Microplex**: Hyams, Walker, Shapiro; ...)

Sept.1985: Proposal to add SVD to Mark-II (Adolphsen et al.)

Layout: „Coke Can"



Impact parameter resolution ~20 μm

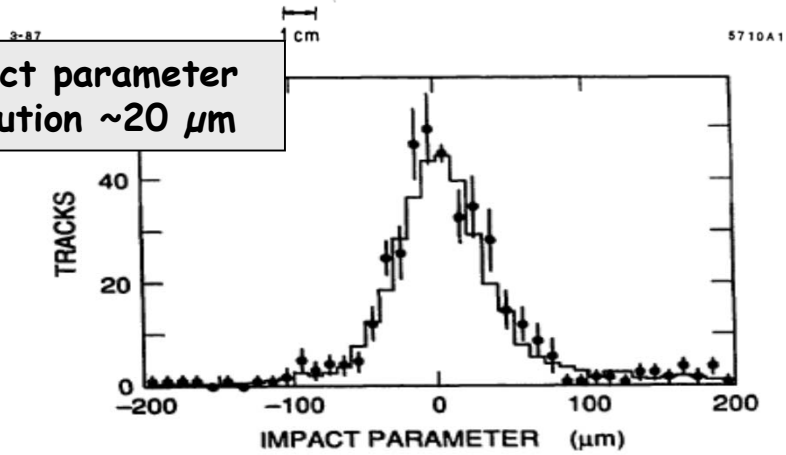
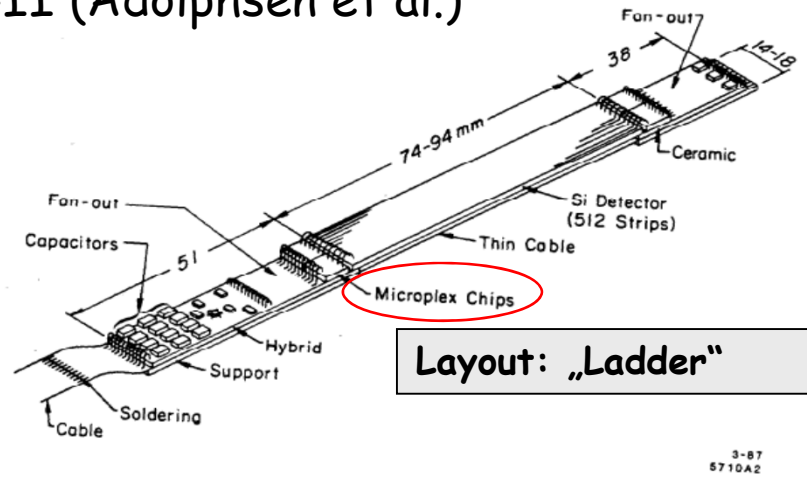
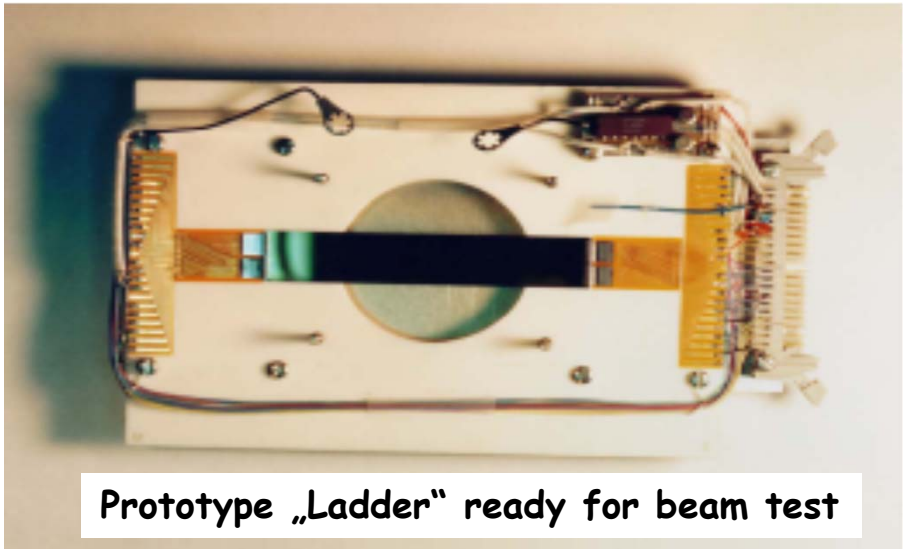


Fig. 40. The impact parameter measurement relative to the single-event vertex, for tracks with transverse momenta above 3.5 GeV/c. The points represent the measured tracks, the histogram shows the results of a detailed Monte Carlo simulation.

Layout: „Ladder"





Prototype „Ladder" ready for beam test

From MARK-II to LHC

Following the pioneering success of MarkII → Si vertex detectors for all 4 LEP-detectors, TeVatron, B-factories, HERA, RHIC and → **LHC**

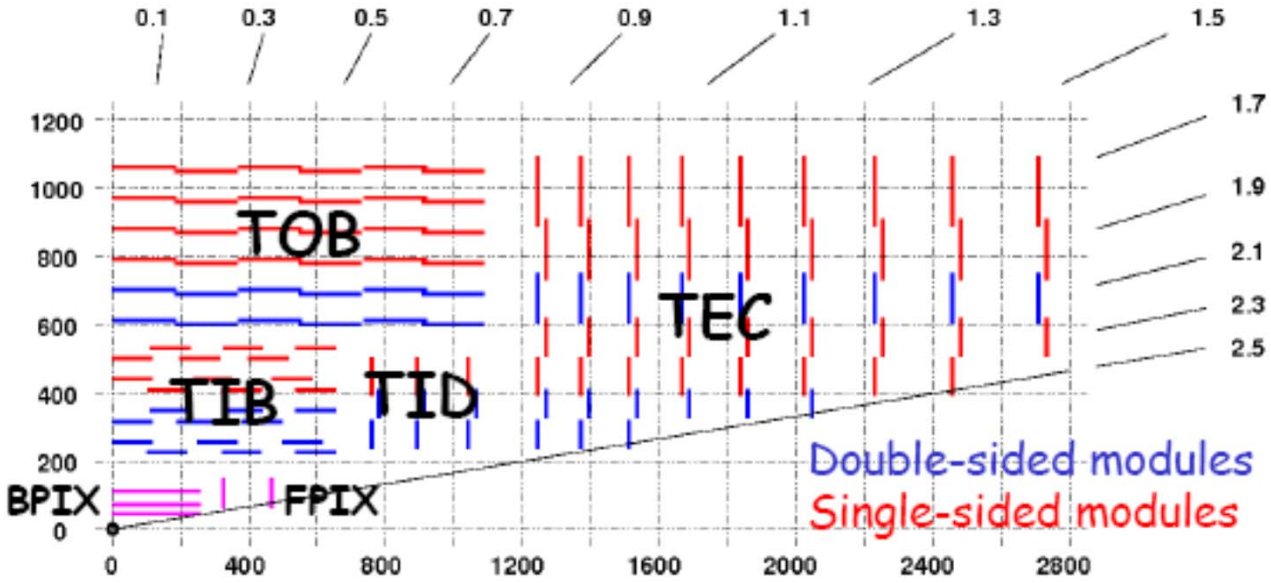
Example: **CMS Tracker** the largest Si tracker ever built!
precision tracking in the harsh LHC environment for $|\eta| < 2.5$

Strip detectors:

- 9.3 M channels
- 210 m^2 sensor area
- 10 barrel layers
- 9 (+3) endcap disks

(Hybrid) Pixel detectors:

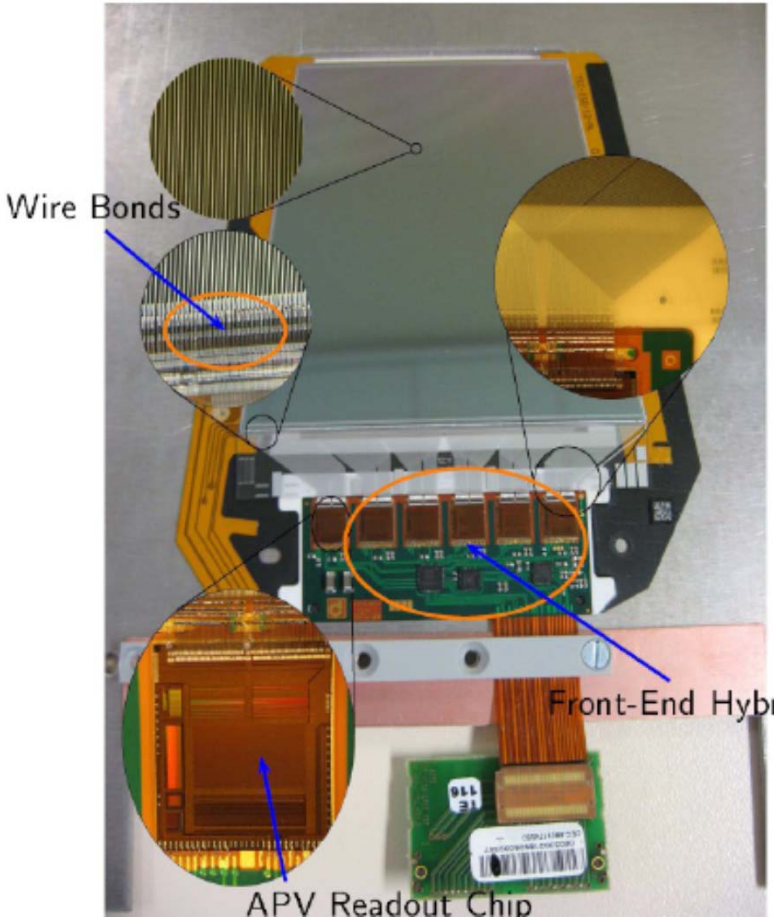
- 66 M channels
- ~1.1 m^2 sensor area
- 3 barrel layers
- 2 endcap disks
- innermost layer at r=4.3 cm

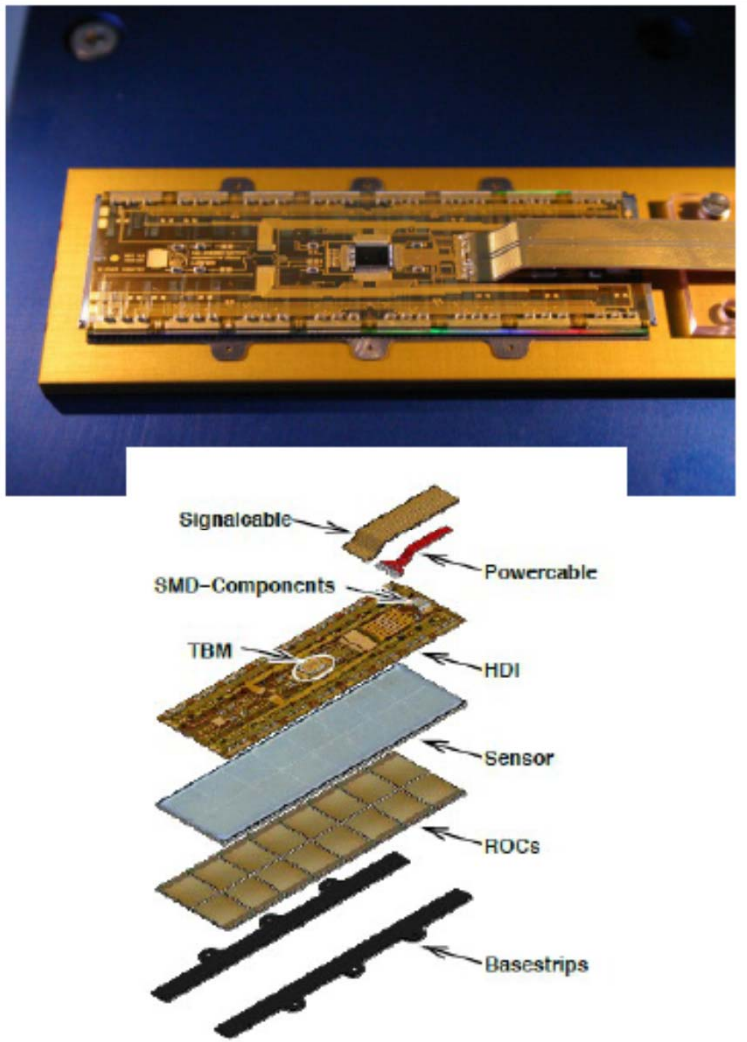


Tracker is running with
97.8 % strips and **96.5 % pixels** operating
at design resolutions and efficiencies

CMS Tracker

The building blocks of the **Si-strip** modules and **Si-pixel** modules

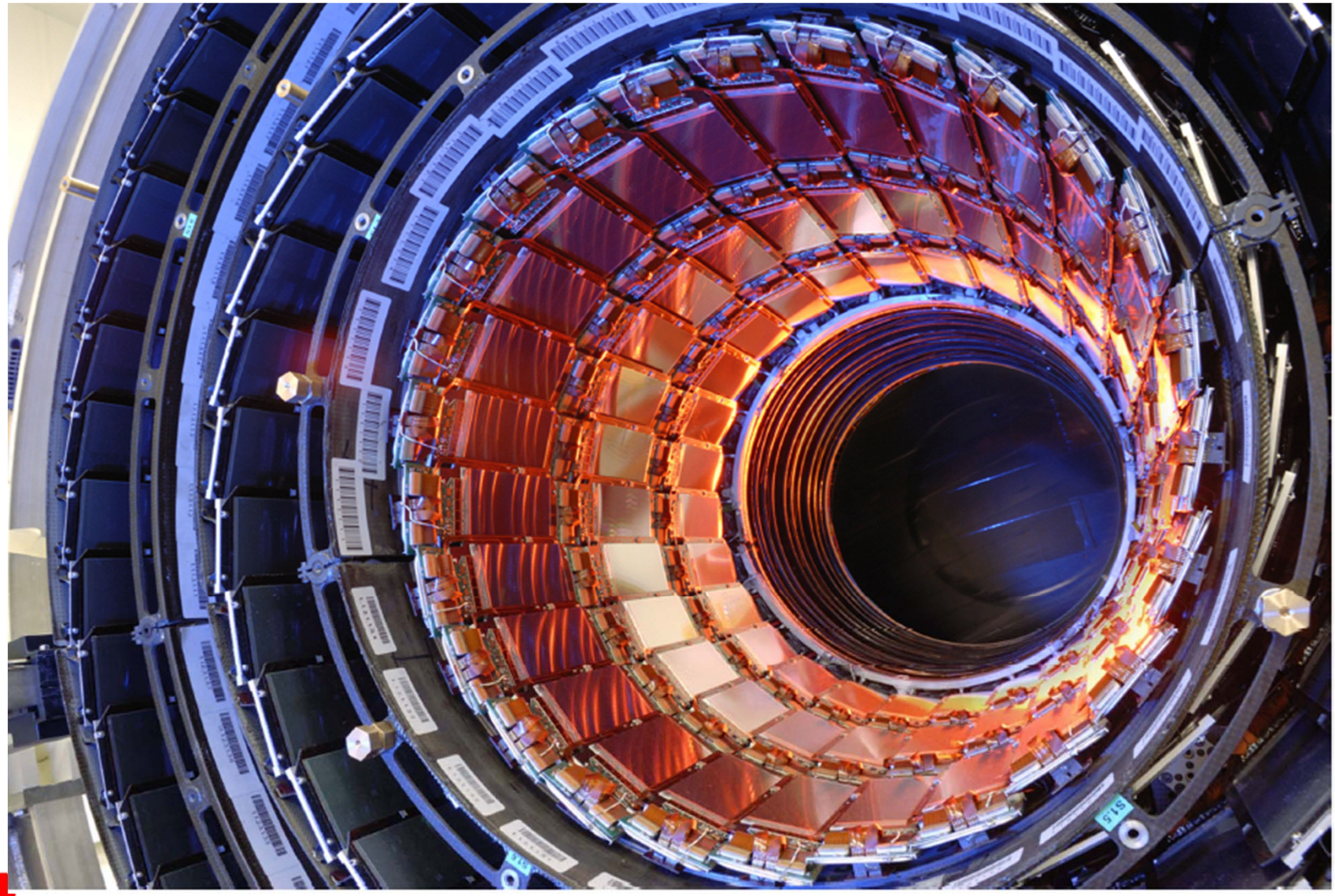




Quasi-industrial assembly (quality control!)

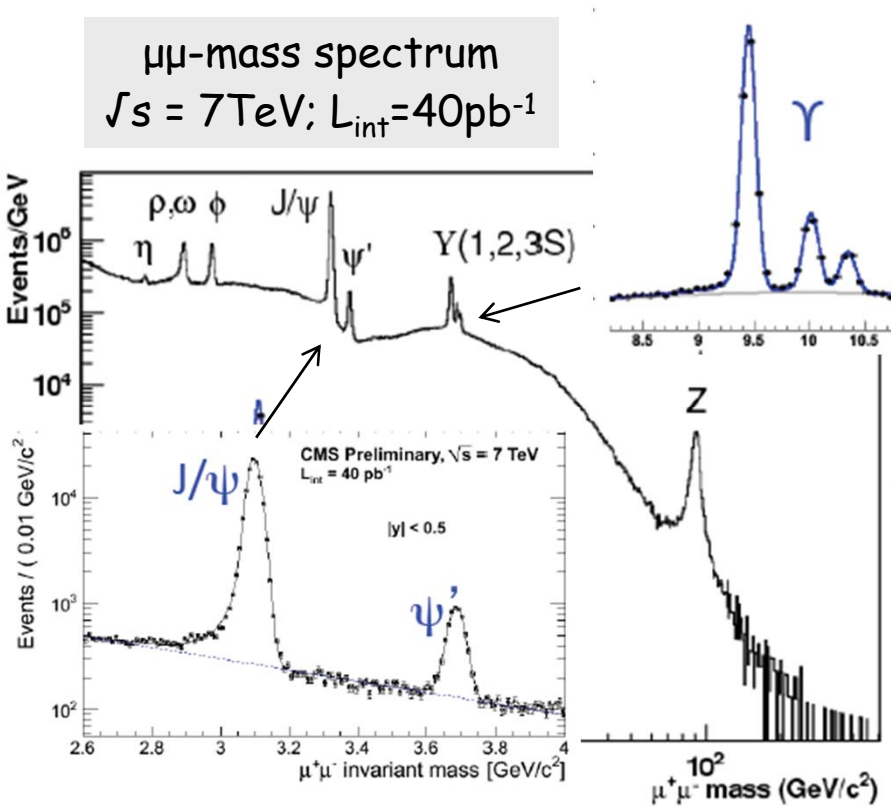
CMS Tracker – "The non-sleeping Beauty"

View of the CMS Tracker during installation in 2007



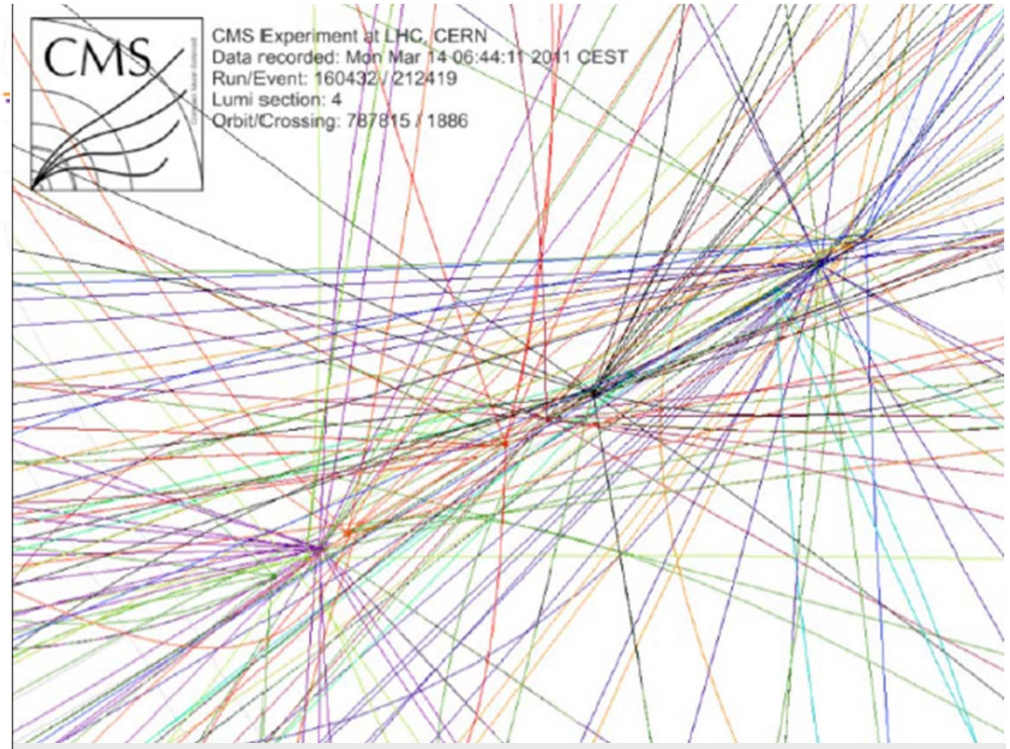
CMS Tracker: Producing Physics Results

μμ-mass spectrum
$\sqrt{s}$ = 7TeV; L_{int}=40pb^{-1}



Some of the challenges:

- events with many interactions/ bunch crossing (@ 25 ns)
- Particle densities in heavy ion interactions
- radiation damage



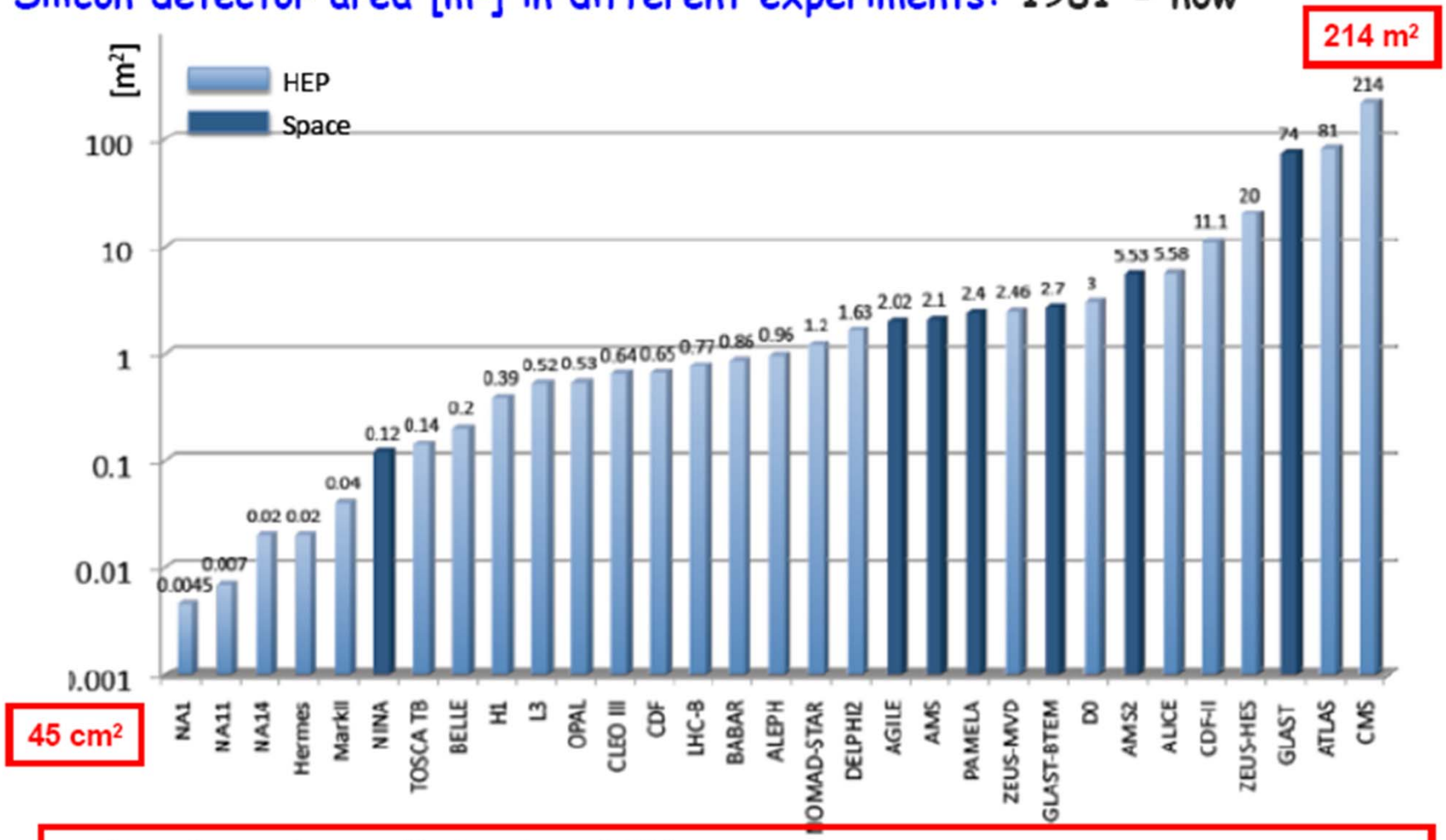
13 interactions within 1 bunch crossing !

LHC machine +experiments:

- verified Standard Model,
- ready for New Physics

Silicon Detectors in hep and Space Experiments

Silicon detector area [m²] in different experiments: 1981 - now



- ~5 orders of magnitude since 1981
- Si detectors are used in (practically) all hep- and in many space-experiments

Si-Strip Detectors for X-ray Science

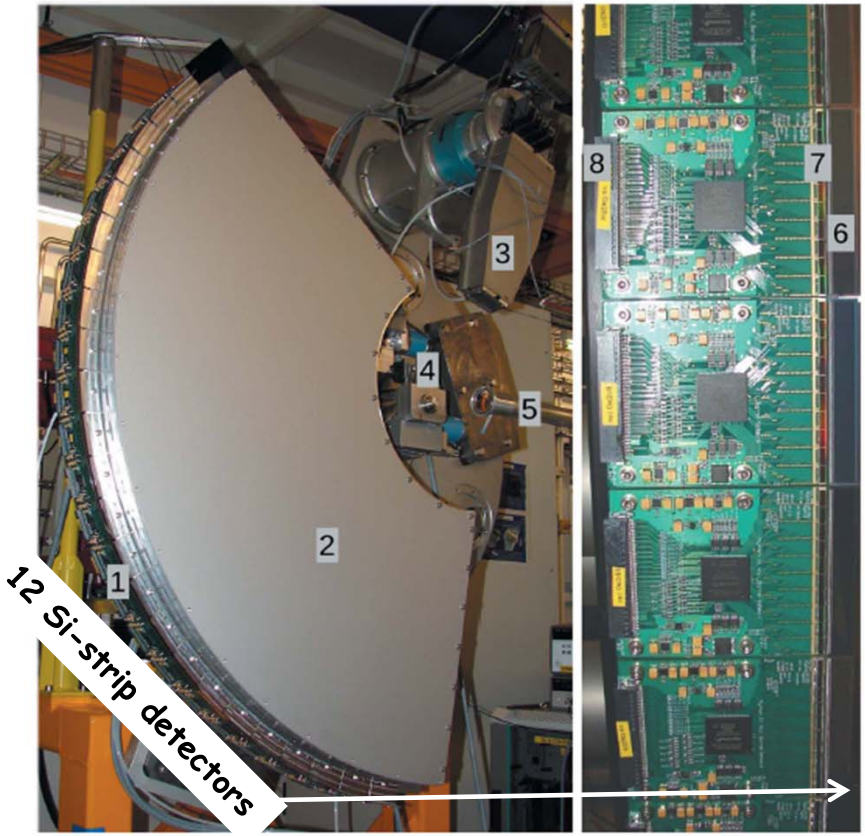


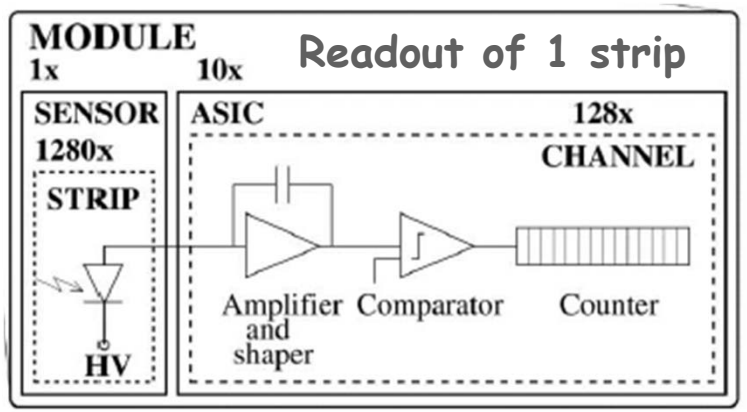
Figure 1
(*a*) Photograph of the MYTHEN detector installed at the powder diffraction station at the SLS and (*b*) a zoom on the modules building the detector. The numbers indicate the main elements of interest: (1) MYTHEN detector layer; (2) He-filled box behind which is fixed the data acquisition system; (3) analyzer crystal detector; (4) center of the diffractometer; (5) beampipe; (6) silicon microstrip sensor; (7) front-end electronics; (8) connector to the data acquisition system.

B.Schmitt et al., NIM-A 501(2003)267

Just one example: **MYTHEN (PSI)**

Si-strip sensors: 320 µm thickness
1280 8 mm long strips with 50 µm pitch

- counting rate: > 2×10^6 per strip
- max. no counts 24 bits (16,777,216)
- energy range 5keV (90%) – 30 keV (8%)
- frame rate: 25Hz (24bit) – 500Hz (4bit)



A highly successful example:

- reduction of measurement time for powder diffraction by ~10,000

→ acquire data before radiation damage

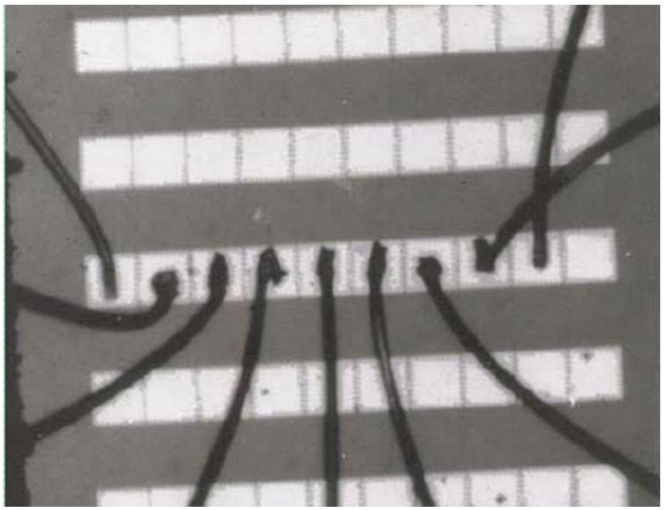
→ time resolved measurements possible

Pixel Detectors: Invention and Principle of CCD

2009 Nobel prize: **W.S.Boyle** and **G.E.Smith**

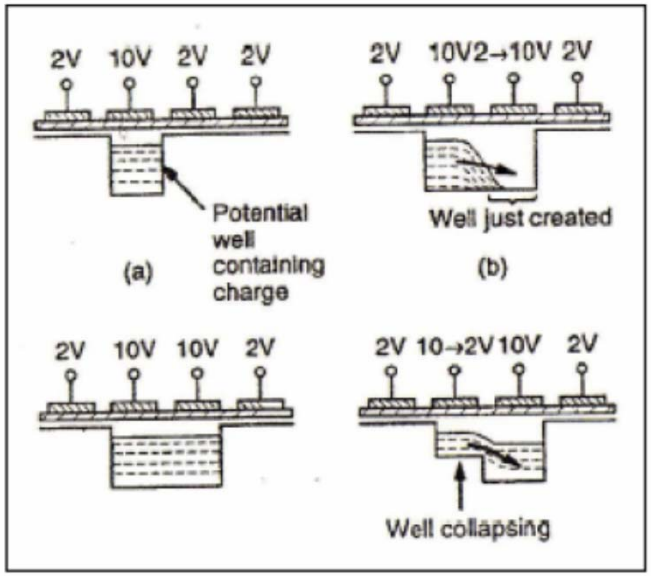
Invention Charged Coupled Device, the first (practical) solid state imaging device

Test device
1 week
after idea!
(1970)

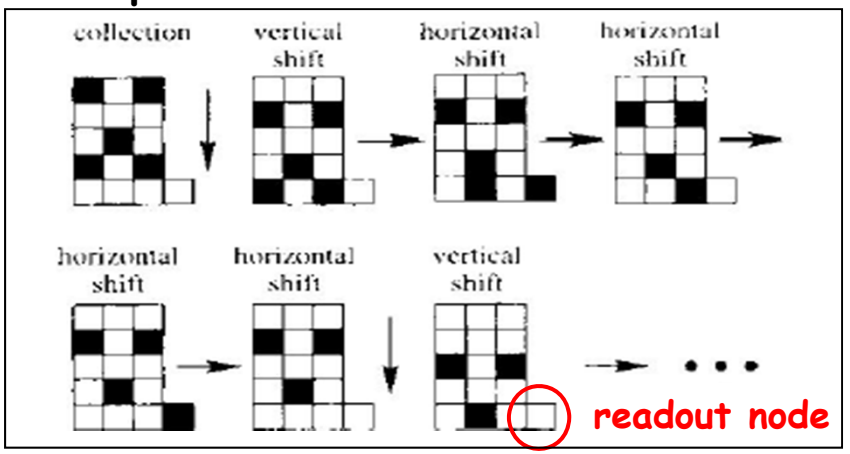


Picturephone
+ CCD inventors

Principle of charge shift



Shift pattern for 2-d CCD



G.E.Smith NIM-A 607(2009)1

CCDs as Pixel Detectors for Photon Science

Use of CCDs for imaging pioneered by **astrophysics**

- high sensitivity compared to film
- low noise (few electrons when cooled)

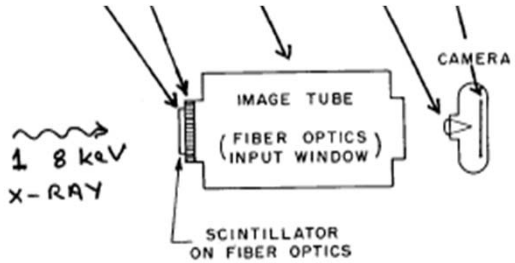
For X-rays: external scintillator → record image

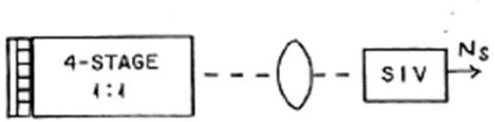
Starting point: scintillator → X-ray film

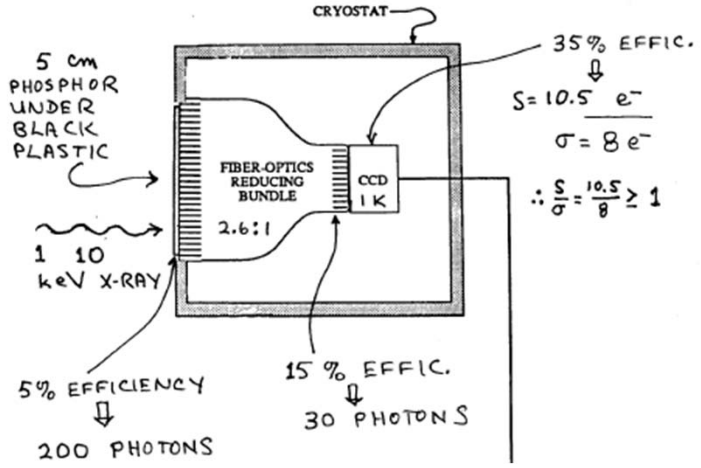
1968 → image intensifier → photogr. film

1978 → image intensifier → Vidicon(s) → Si Intensified Target → Image Plate

1997 → fiber optic bundle → CCD



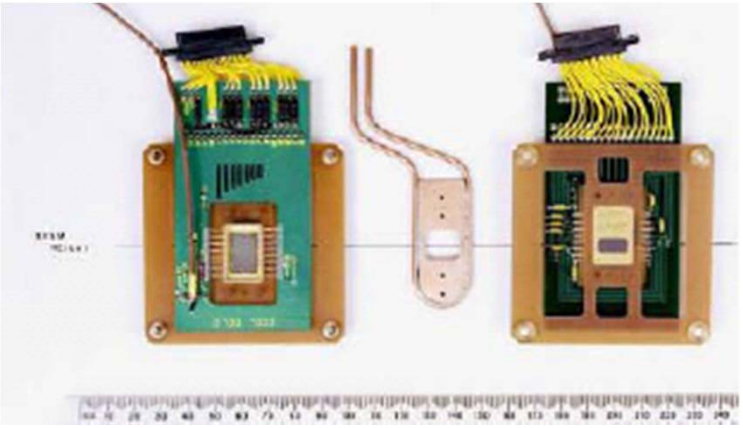


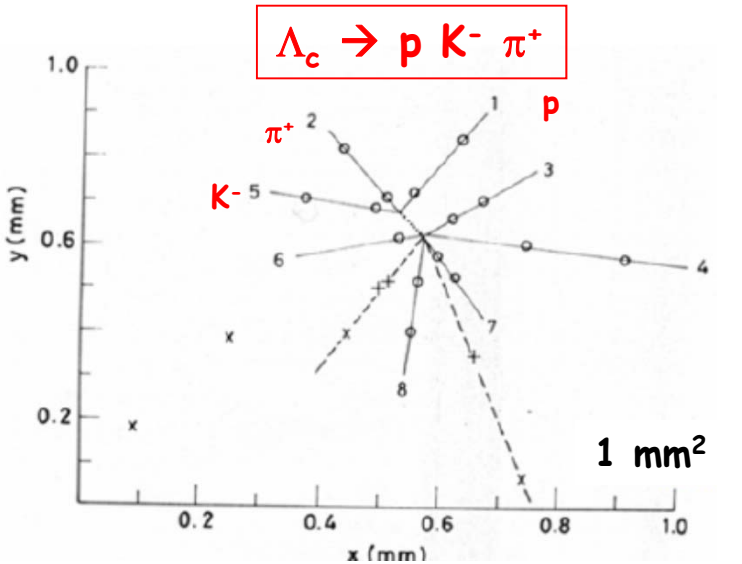


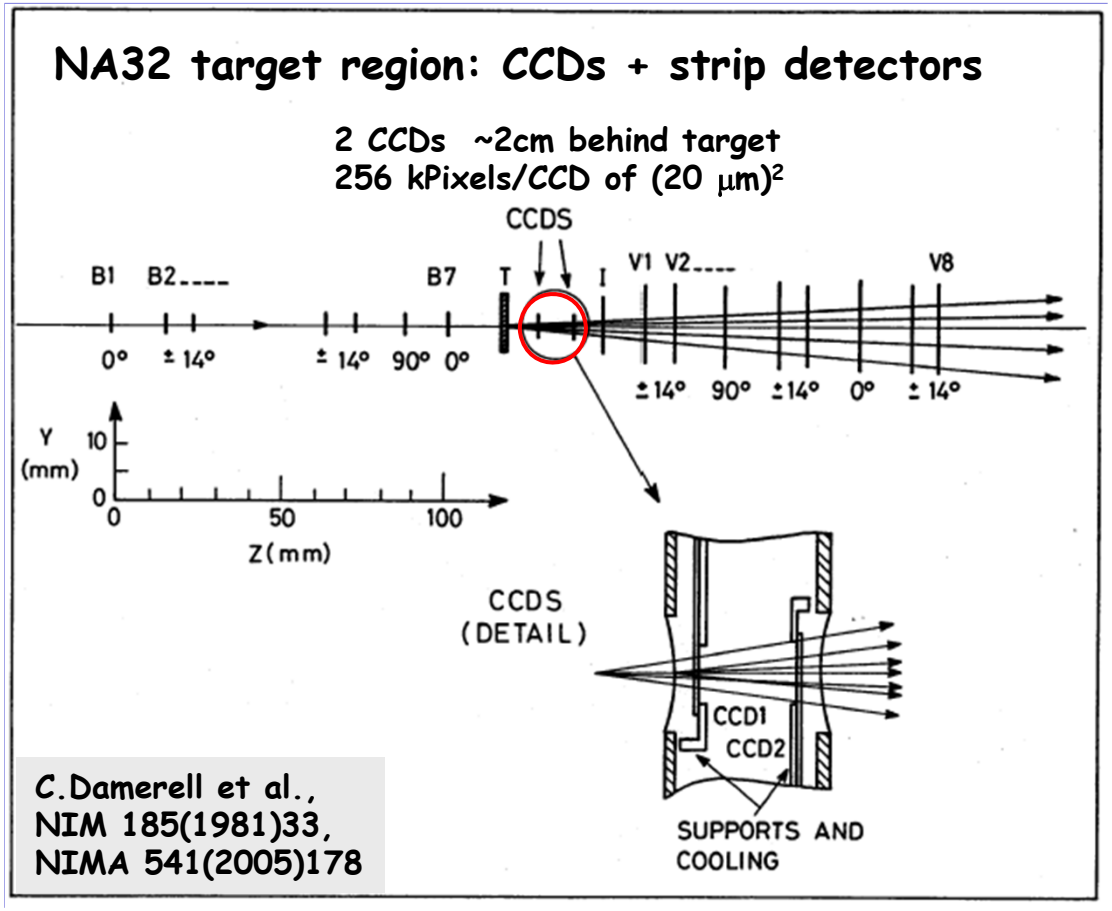
S.M.Gruner, Transaction ACA 34(1999)11

Gain in sensitivity (measurement time) by **many orders of magnitude** and in **data quality** (PSF – Point Spread Function)

CCDs as Precision Position Detectors in hep







→ superior pattern recognition convincingly demonstrated

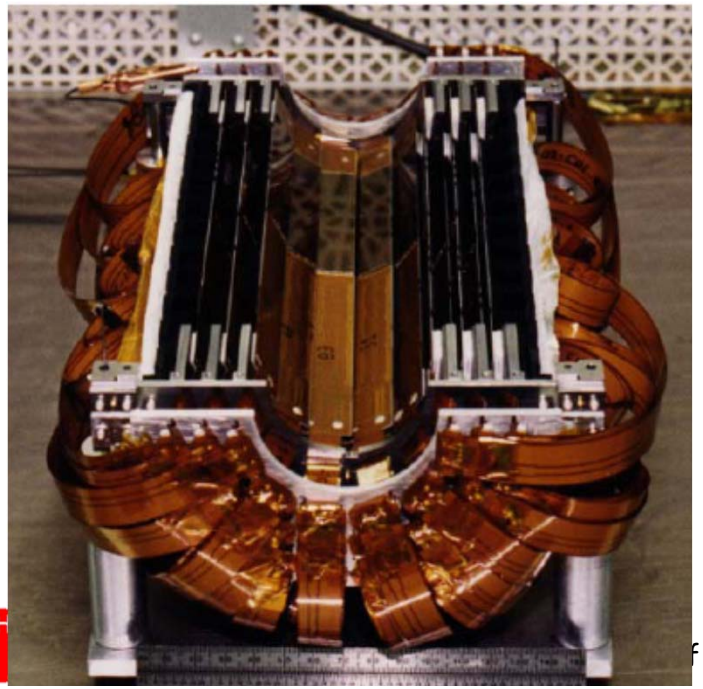
→ C. Damerell et al. join SLD@SLC to build **the best vertex detector** built so far (with respect to resolution and material budget)

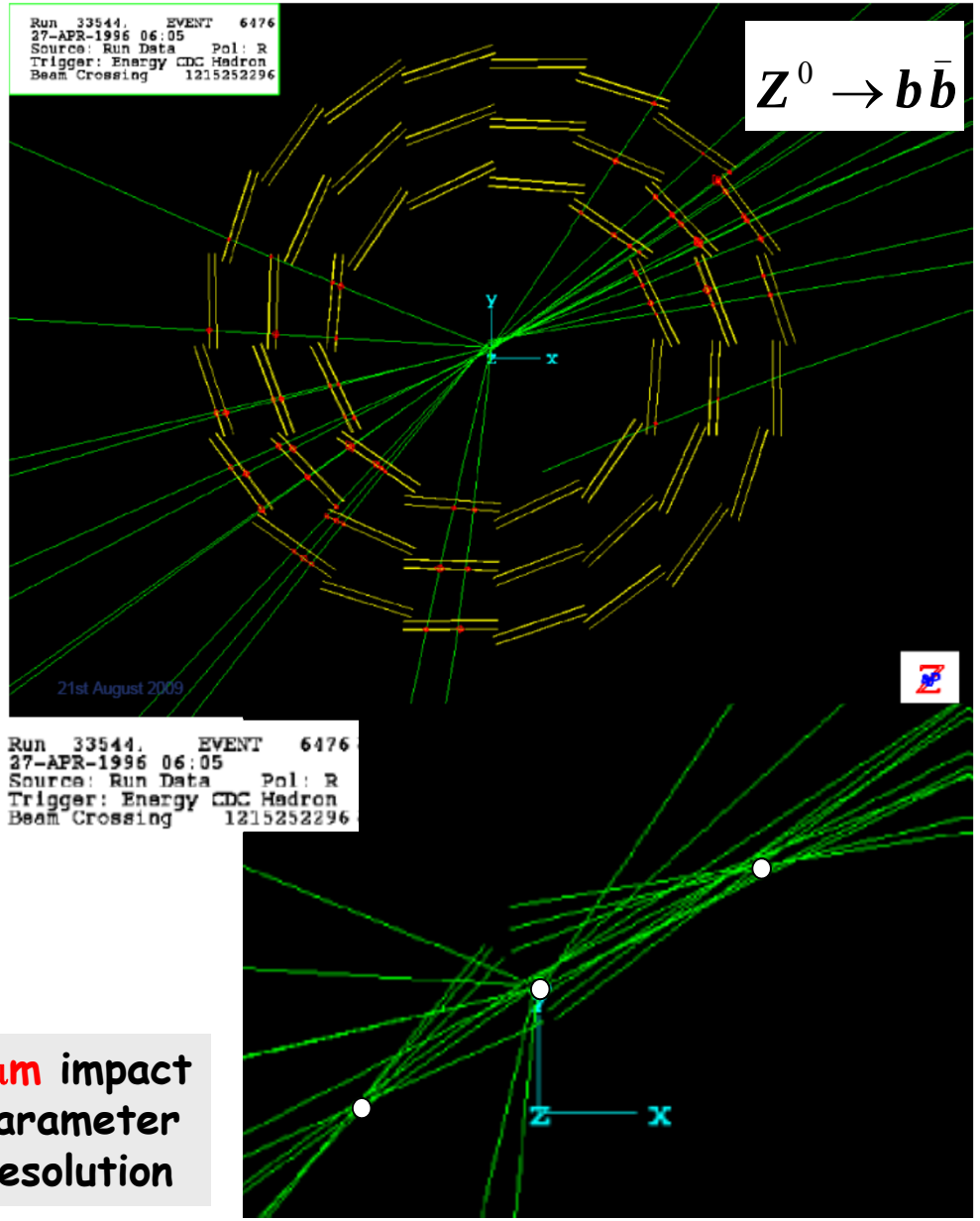
CCDs: VXD3 Vertex Detector for SLD@SLC

VXD3@SLD

- -installed in 1995
- -307 MPixels (ATLAS: 80Mpixels !)
- -0.4% X_0 (multiple scattering)
- -1st layer < 3cm from beam)

By far most performing vertex detector in terms of resolution
→ reference point for ILC vertex detectors



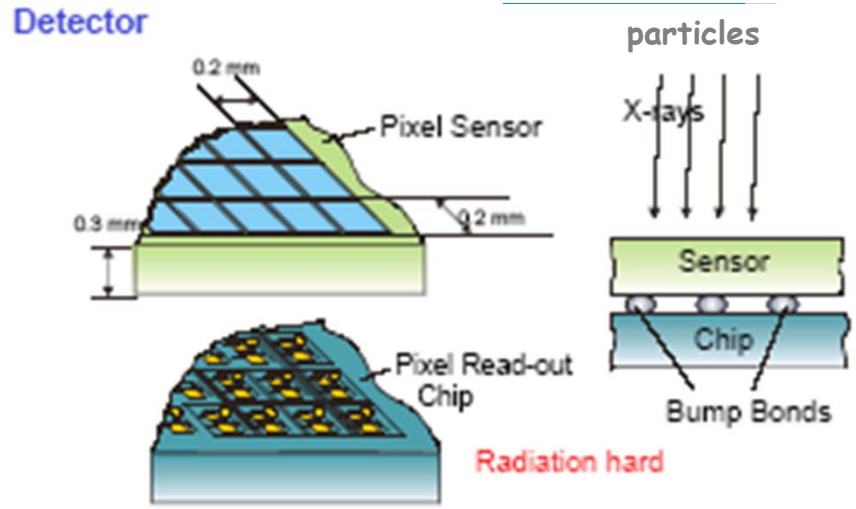


8μm impact parameter resolution

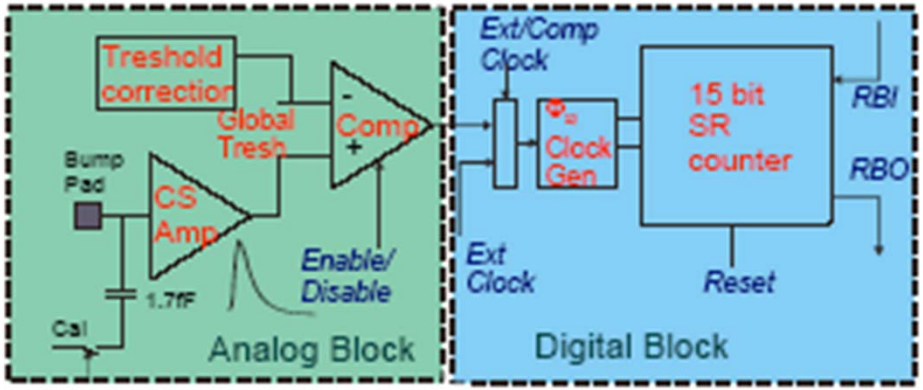
Hybrid Pixel Detectors

Idea: separate sensor and electronic → flexibility **but** additional material

Concept:



Pixel electronics (just one example)



Special features:

- read-out chip directly mounted on top of detector by bump bonding
- every pixel has its own electronics
- technology for electronics and sensor can be chosen separately (eg high-Z sensor + Si readout; optimize for radiation hardness,...)

Limitations:

- amount of material for precision vertex detector (multiple scattering!) also power dissipation – cooling
- read-out speed and dynamic range (in particular for X-ray science)

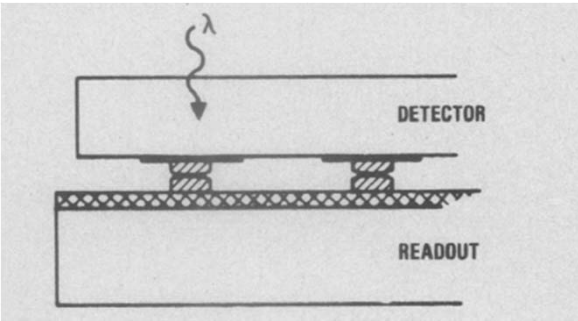
Hep experiments using hybrid pixels:

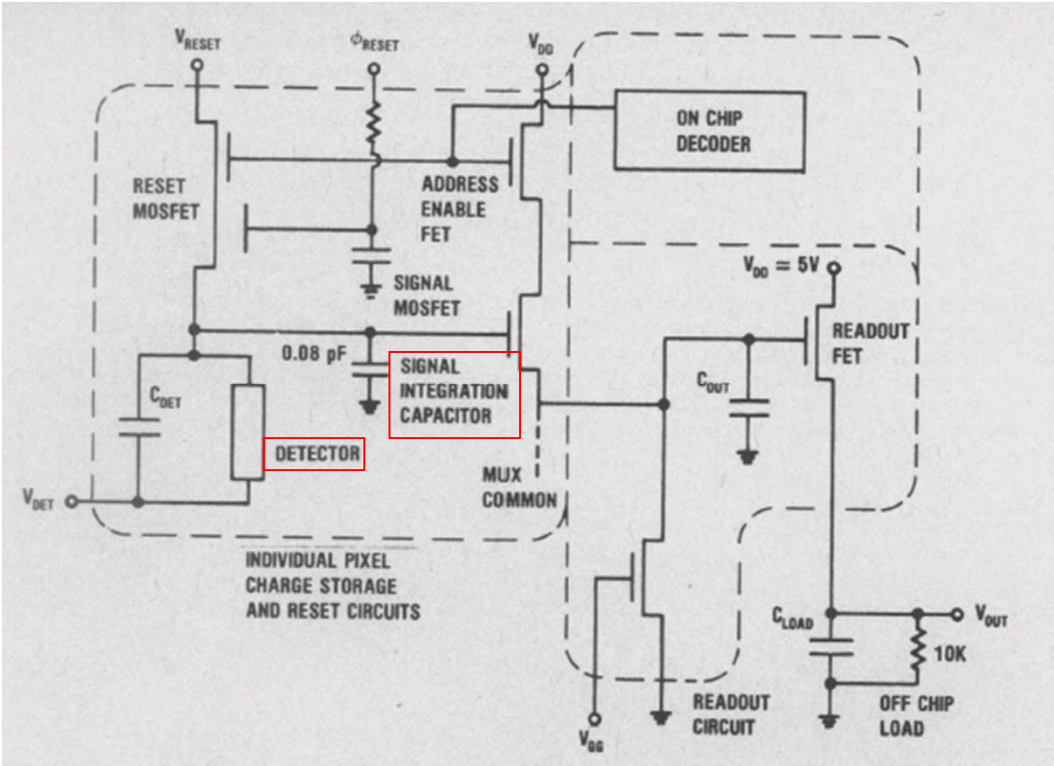
- CMS (66 Mpixels of 150×100 μm^2)
- ATLAS (80 Mpixels of 40×400 μm^2)
- ALICE, PHENIX (BNL), FAIR-expts. (PANDA, CBM, ...) ...

Early Hybrid Pixel Detector for X-rays

First Ge pixel detector in 1961
G. Dearnaley

S.Gaalema at 1984 IEEE-NSS





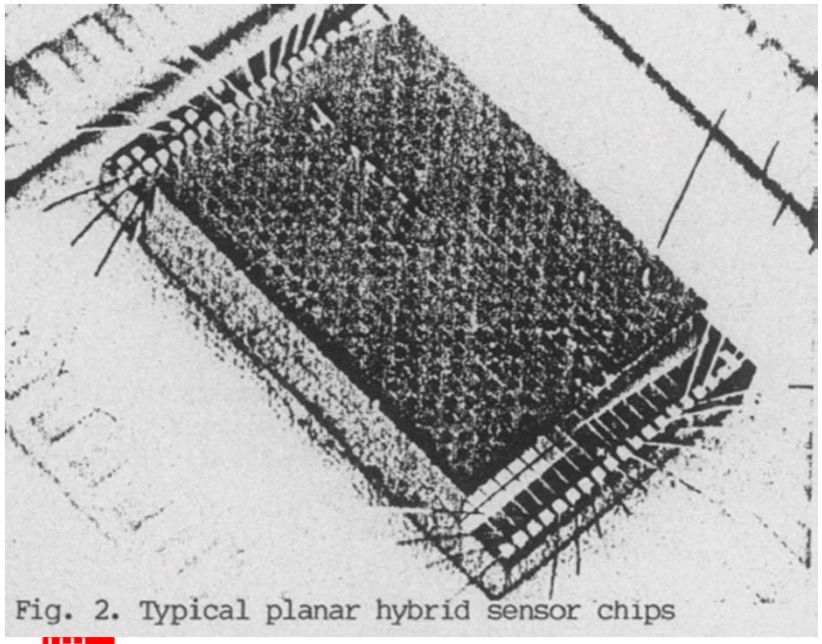


Fig. 2. Typical planar hybrid sensor chips

Performance:
- 600×600 pixels (20 μm)²
- 50 e (rms) noise
- random access to every pixel
- average power 1 μW/pixel (for 1kHz readout)

was used to read out **Si** and **Ge** detectors

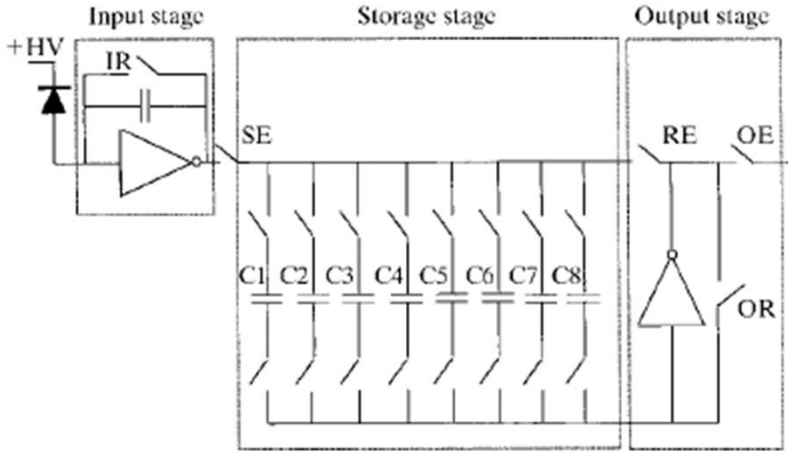
S.Gaalema IEEE Trans. NS-32, No.1(1985) 417

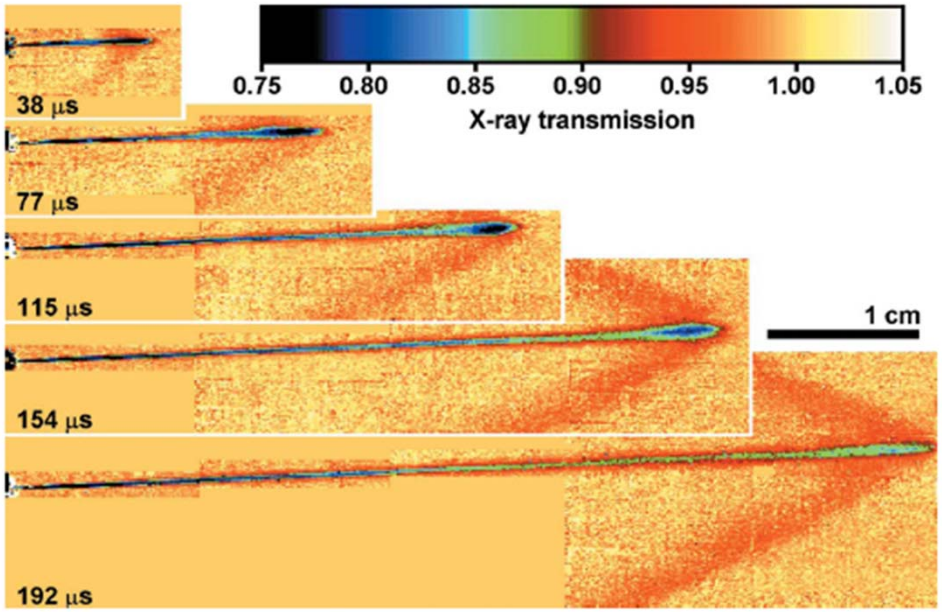
Charge Integrating Hybrid Pixel Detector for X-rays

Task: Fast time resolved imaging with **µs frame rate** → counting not an option
→ **integrating readout**

Application:
µs time-resolved x-ray radiography of multi-phase, direct-injection gasoline fuel spray
→ **Verify fluid dynamics simulations**

Single pixel readout architecture (group S. Gruner)





Specifications and performance:
- Si: 92×100 pixels, (150 µm)^2; 300 µm thick
- 8 storage cells; min. integration time 1 µs
- capacity: 17,000 8.9keV X-rays
- non-linearity <0.2% (full range)
- noise: ~20 keV (X-rays)
- 1.2µm HP process; GEC-Marconi bump bond
- 100 µW power/pixel
- limited radiation hardness

G.Rossi et al J.Synchr.Rad 6(1999)1096

Supersonic jet of Diesel fuel spray in 1atm SF_6
- image area (61.7×7.5) mm^2 [built-up from images (13.5×2.5) mm^2]
- shockwave: increase in gas density ~15%

MacPhee et al., Science 295(2002)1261

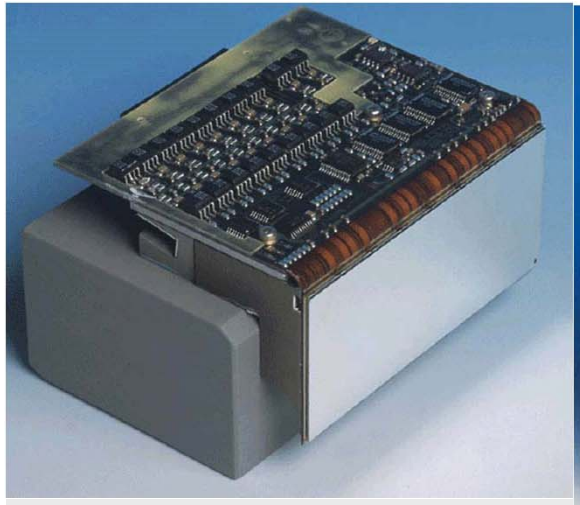
X-ray Counting Hybrid Pixel Detector(s)

Several examples: Medipix1, Medipix2, Medipix3, PILATUS1, PILATUS2, ADSC,…
development chains → continuous improvements + profit from technology advance

Example: PILATUS (PSI)- specifications and performance:

- pixelsize: $(172\ \mu m)^2$
- max. rate: 1.5 MHz/pixel
- dynamic range: 20 bits (1,048,576) no noise !
- read-out time: 5 ms
- frame rate: 10-100 Hz

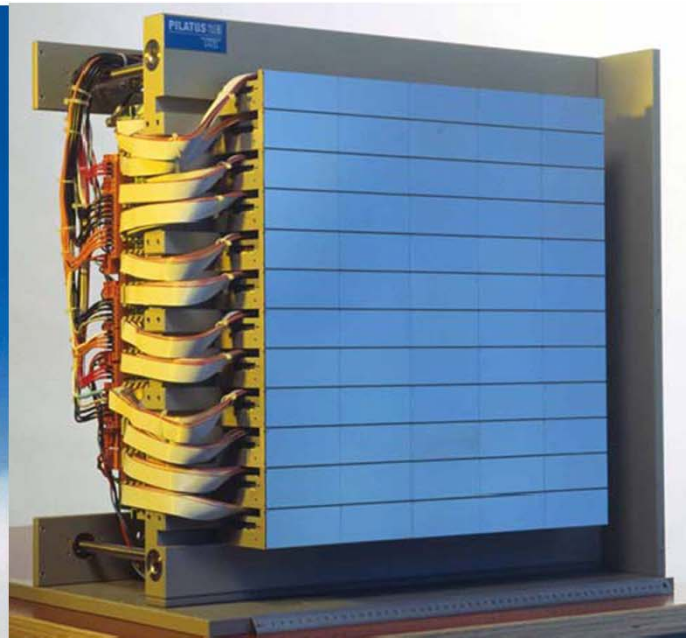
1st generation PILATUS module



B.Henrich et al.,
NIM-A607(2009)247

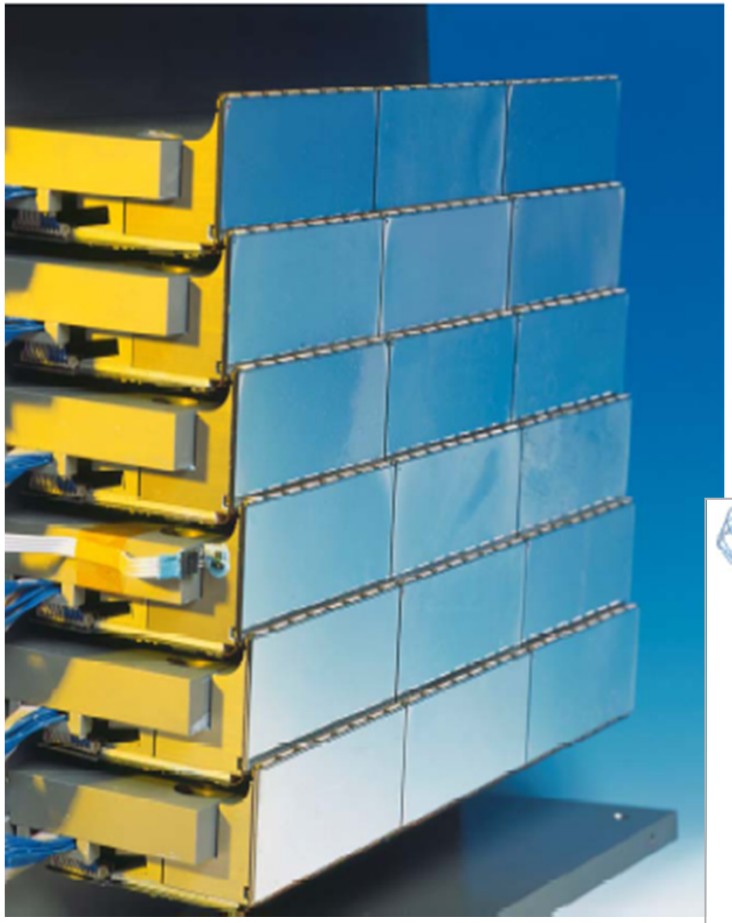
1st generation PILATUS 1M

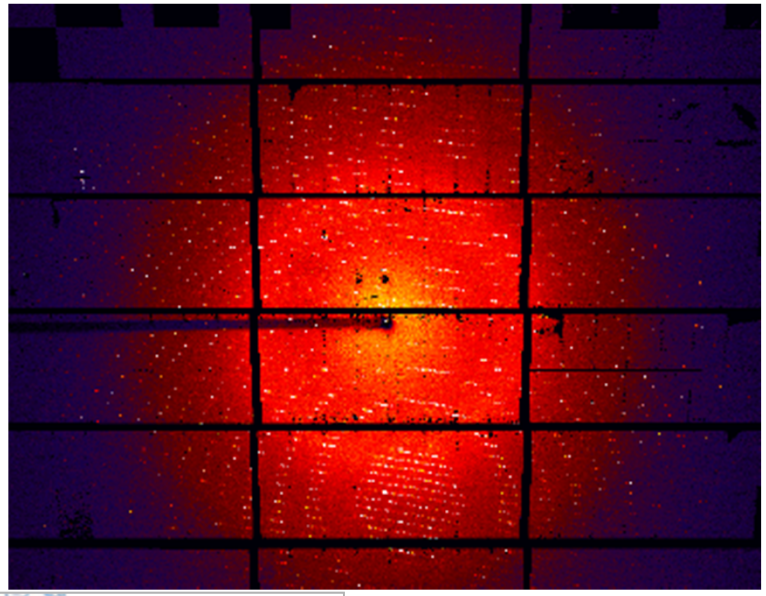
PILATUS 6M

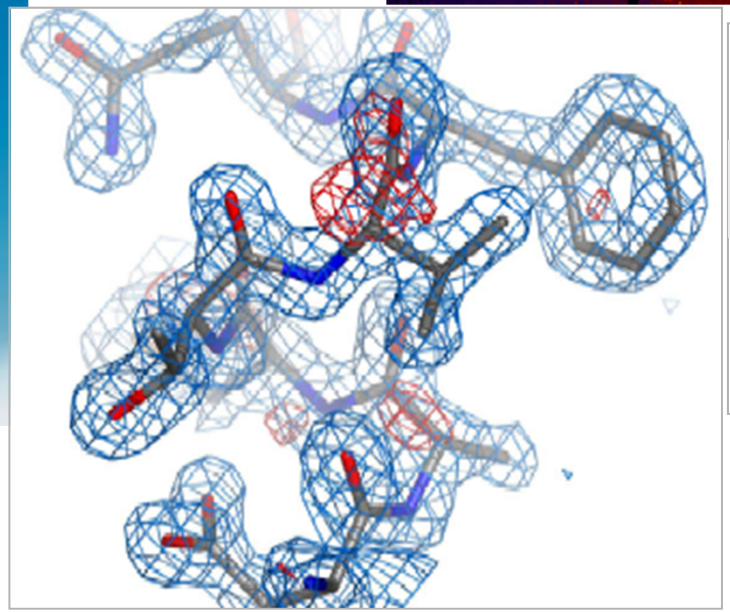


X-ray Counting Hybrid Pixel Detector(s)

Example of an early measurement with PILATUS1







Electron density map of Thaumatin

C. Brönnimann et al., J.Sync.Rad.13(2006)120

Swiss Economic Award to DECTRIS

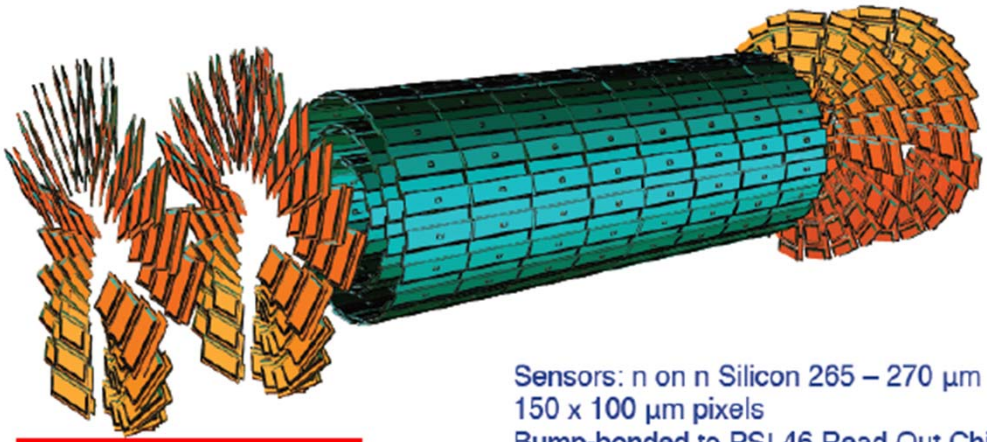
Pixel Detectors in hep

Hybrid-Pixels in use in hep since 1995
needs micro-electronics because of large no. of channels !

- pioneered in fixed target heavy ion expts. at CERN
- e^+e^- colliders (DELPHI)
- pp- and ion-collider; in particular ATLAS,CMS,ALICE

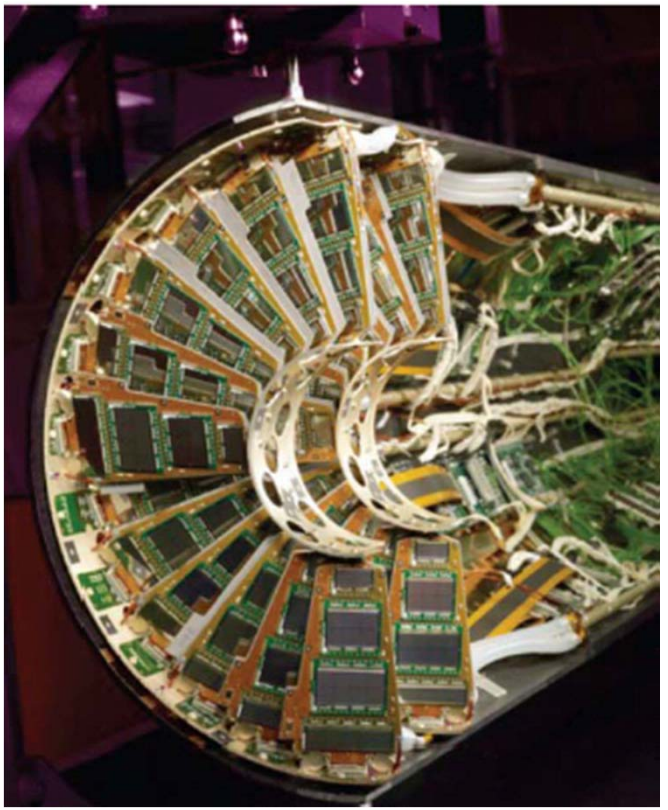
CMS Pixel Detector: 66 Mio. pixels

- 3 barrel layers at 4.3, 7.2, 11.0 cm
- 2 forward disks



Total Area: 0.78+0.28 m²
66 Million Pixels

Sensors: n on n Silicon 265 – 270 µm
150 x 100 µm pixels
Bump-bonded to PSI 46 Read Out Chips



Performance from data: position resolution σ_x = (12.8 ± 0.9)µm; σ_y = (32.2 ± 1.4)µm

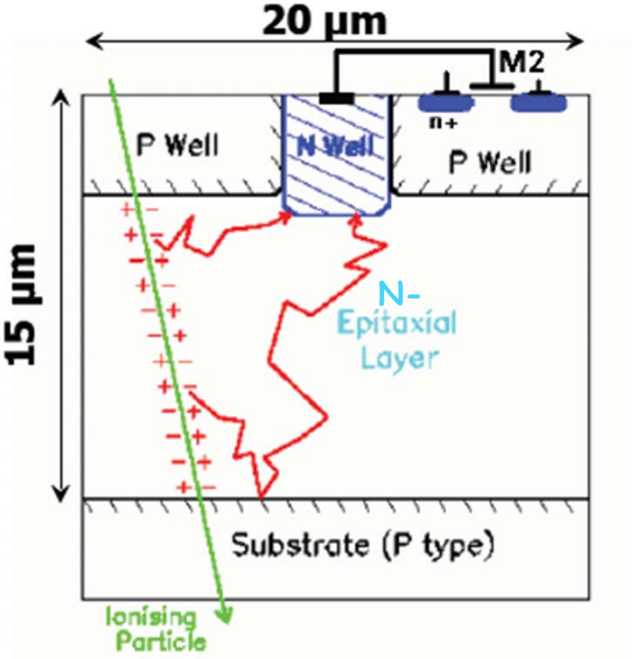
→ design specifications achieved
→ highly efficient b-tagging / secondary vertex recognition in complex environment
→ essential tool to search for New Physics at the LHC

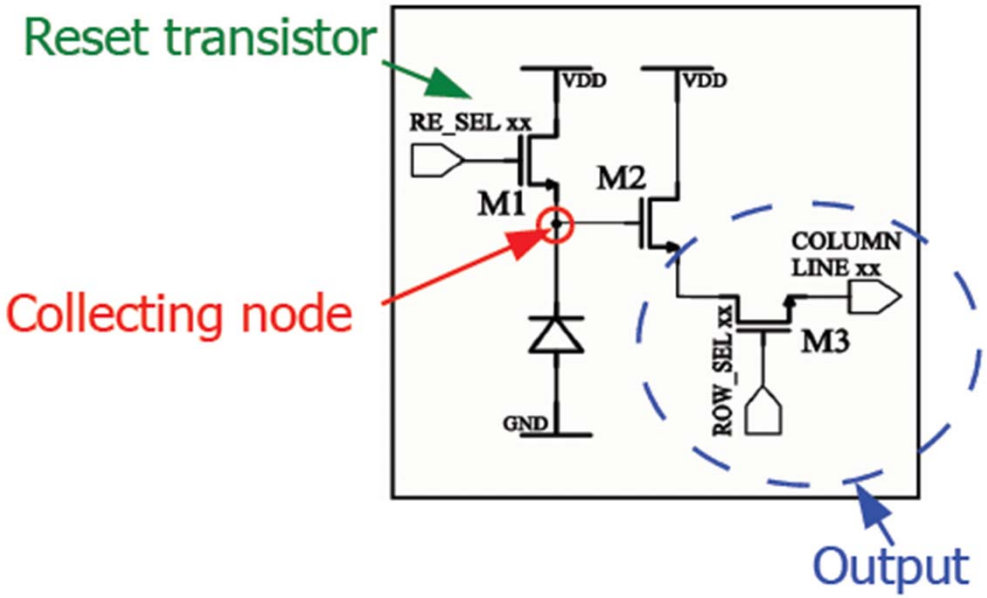
MAPS: Monolithic Active Pixels

For hep: inactive material + sensor thickness → interactions + multiple scattering → degradation of performance (in particular for e^+e^-)

→ monolithic sensor - readout and thinning of substrate

Example: CMOS-MAPS (R.Turchetta et al., NIM-A 458(2001)677)





Outstanding features:

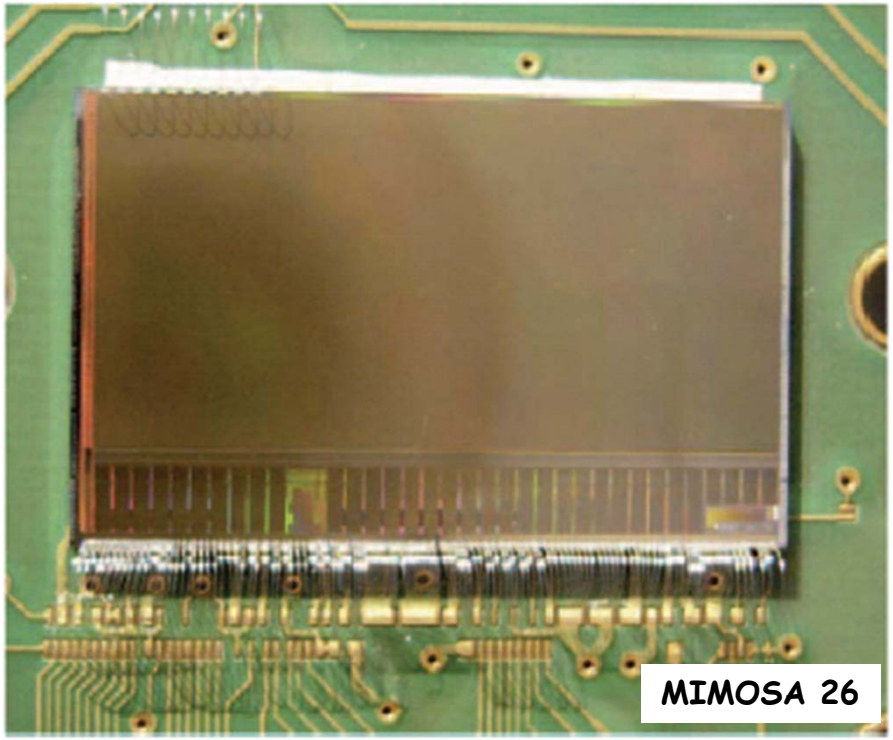
- standard VLSI technology
- small (>10 µm) pixels
- low power
- low noise (5e rms)
- thinned down to 50 µm
- random access

problem: readout time

MAPS: Monolithic Active Pixels

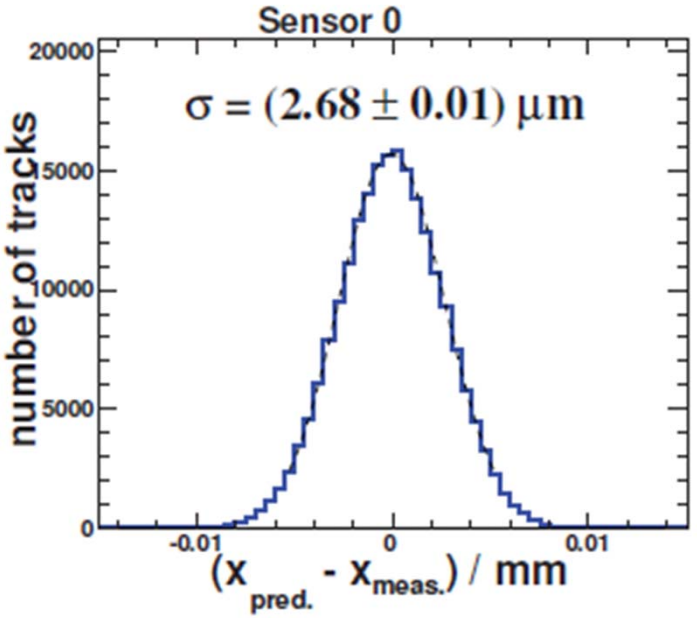
State of the art: MIMOSA-26 (EUDET-telescope)

- 0.35 µm CMOS OPTO process
- 572×1152 pixels of $(18.4\ \mu m)^2$ → 10mm×21mm
- 80 MHz read-out: zero supressed, binary with data sparsification → reduction of data volume by factor 10 – 1000 (depending on occupancy)
- 112 µs integration time



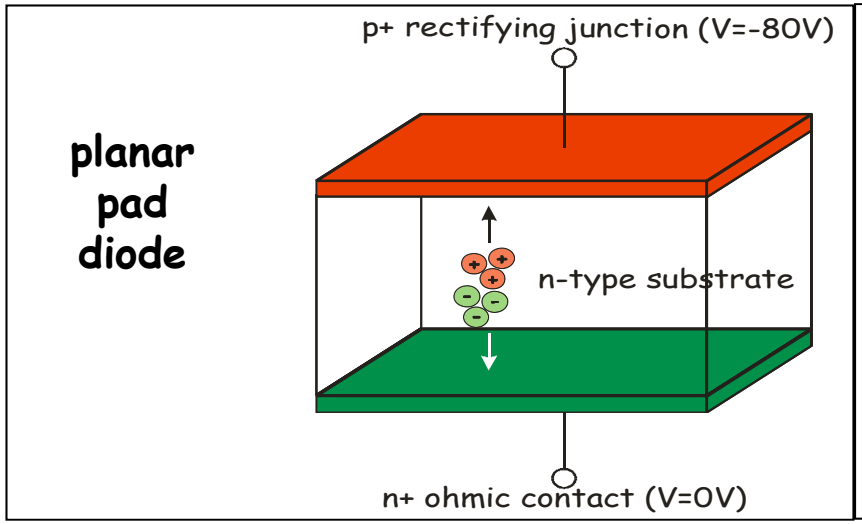
position resolution (CERN beam test)

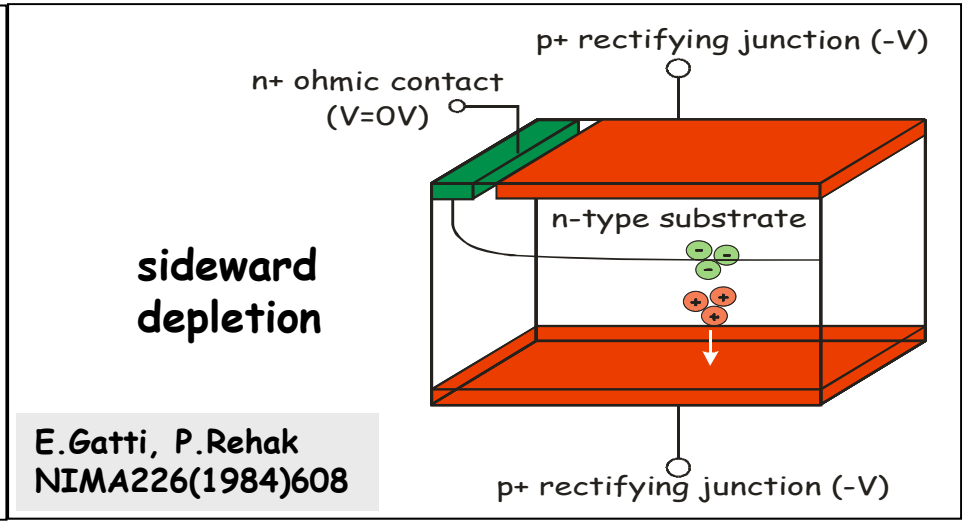
$\Delta x \sim \Delta y \sim 2.7\ \mu m$



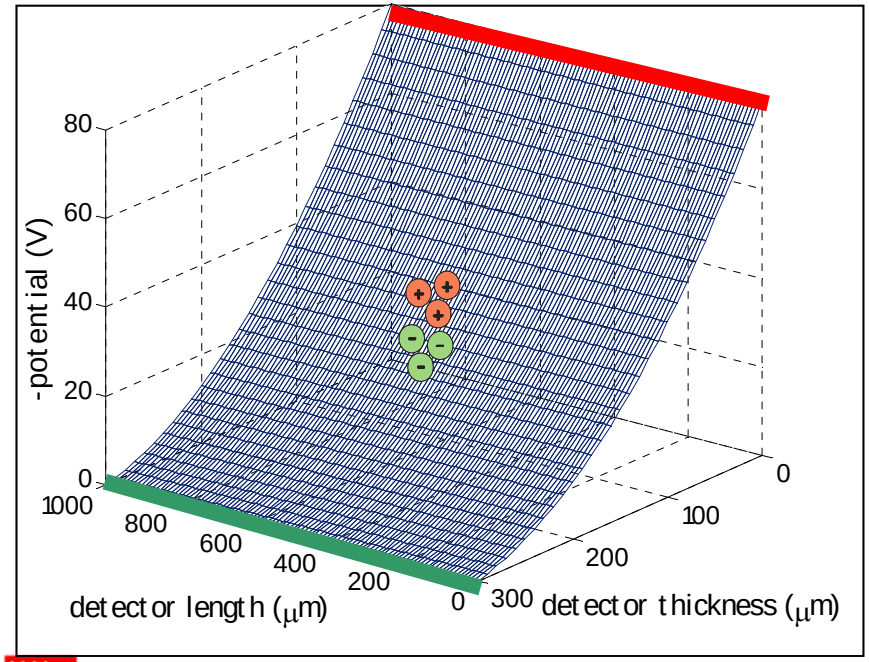
E.Corin, IEEE NS-Conf. N13-118 (2009)816

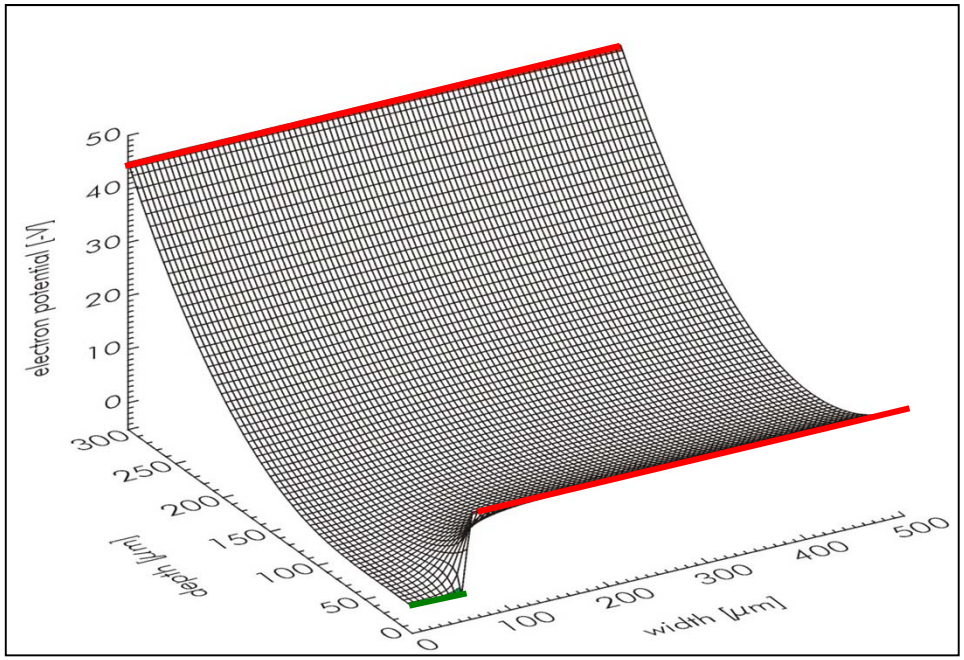
Drift Detectors: The Principle of Sideward Depletion





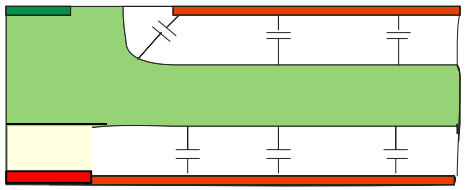
E.Gatti, P.Rehak
NIMA226(1984)608





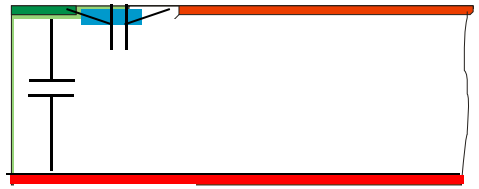
Principle of Sideward Depletion

below full depletion

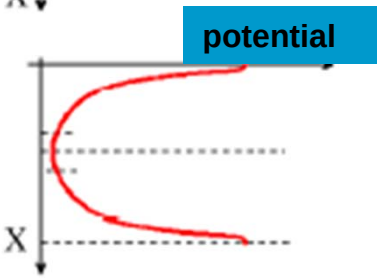


potential

above full depletion



potential



impact on anode capacitance

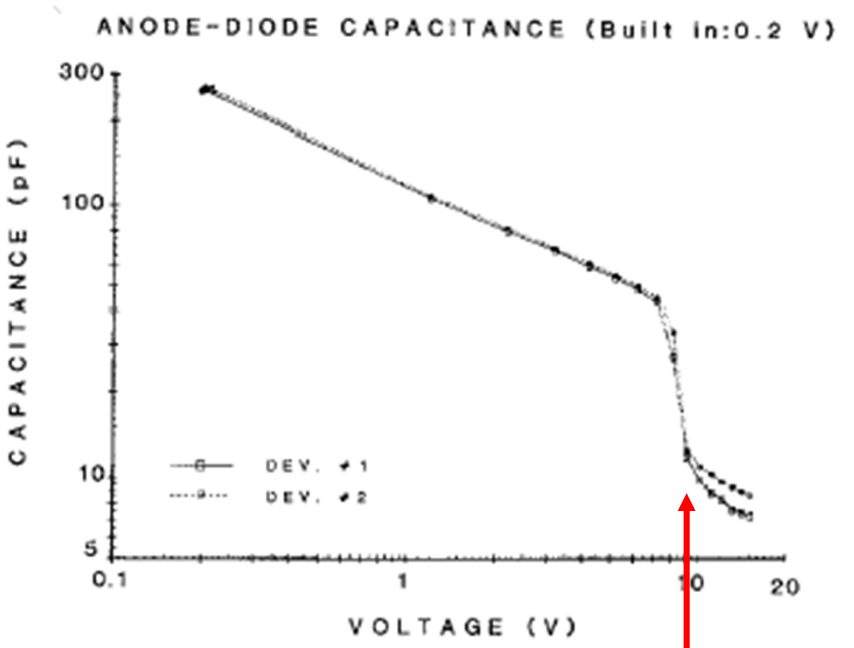


Fig. 12. Capacitance versus voltage plots of two of the test devices provided on the wafer for monitoring its doping uniformity.

P.Rehak et al.,NIMA235(1985)224

full depletion

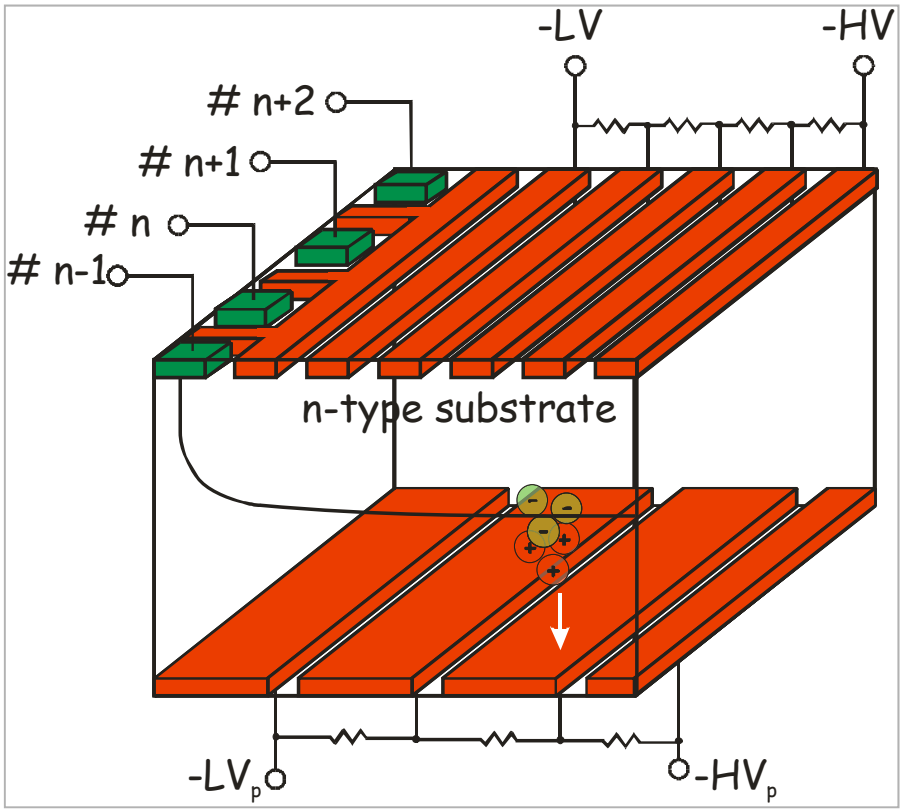
- below full depletion:
  parallel plates
  → C ~ area
- above full depletion:
  - line (or point) - plate
  → C ~ ln(area)

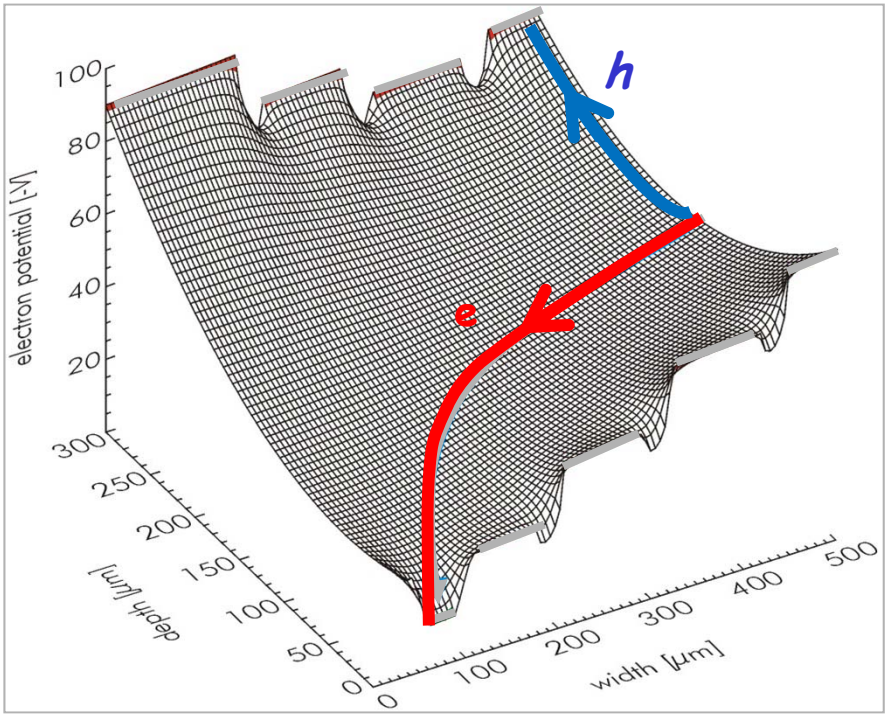
→ collect charge from a large area with minimal capacitance

→ large area low noise detectors feasible

Si Drift Detector as 2-D Tracking Detector

- Cathode strips → drift field
- segmented anode → transverse position – time-of-flight → longitudinal pos.



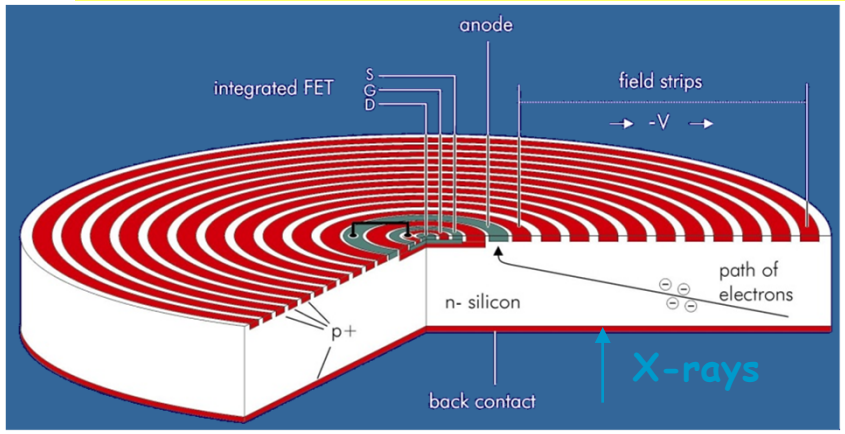


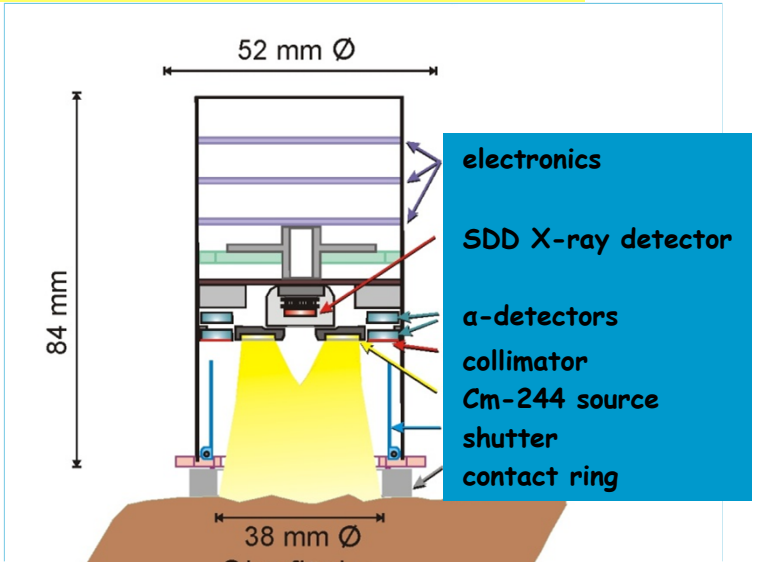
potential (near the anode)...

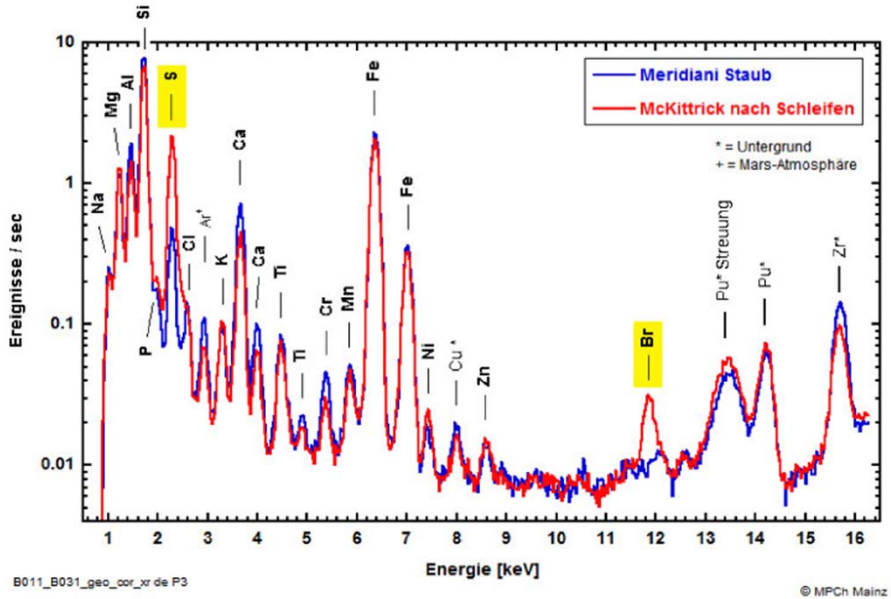
achieved performance: 2 μm in lab (laser light)
10 μm in test beam
18 μm in actual experiment

Emilio Gatti and Pavel Rehak: Silicon Drift Detector SDD

SDD with integrated JFET→ Low Noise X-ray Detector



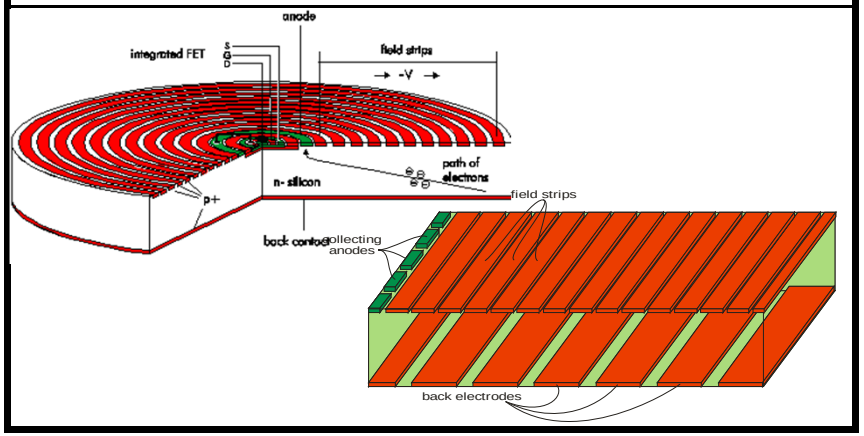




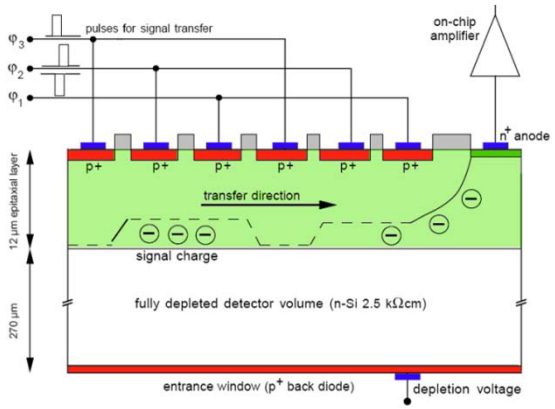
L.Strüder,IEEE-NSS Rome 2004,
R.Rieder, MPI für Chemie, Mainz

The Family of Detectors Based on Sideward Depletion

Silicon drift detector

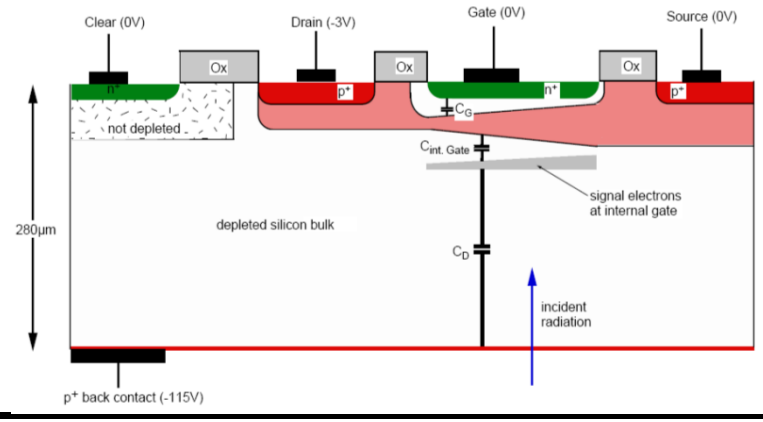


Fully depleted pnCCD

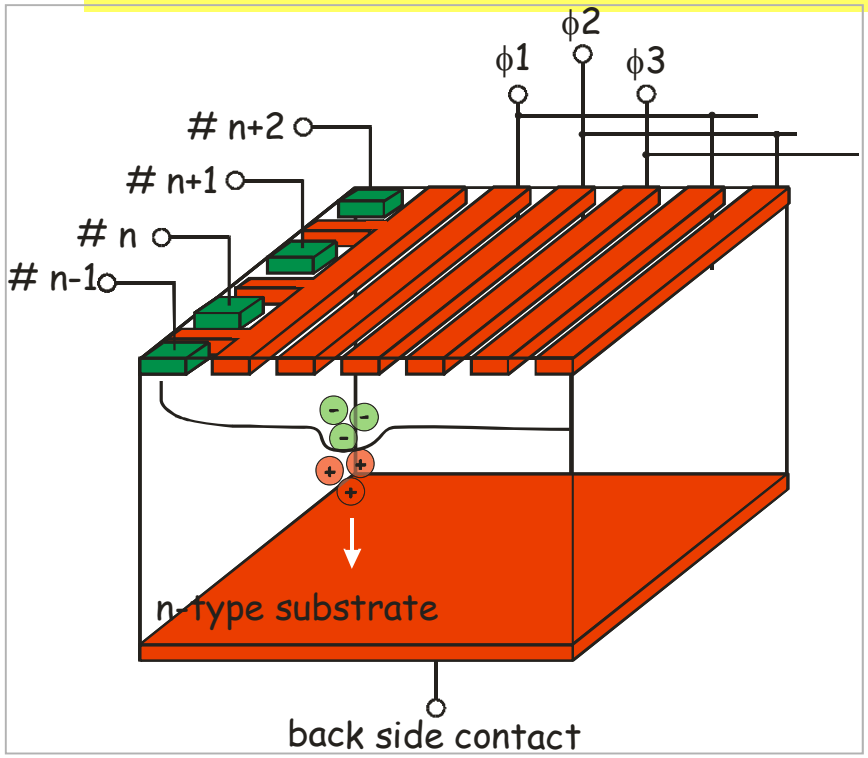


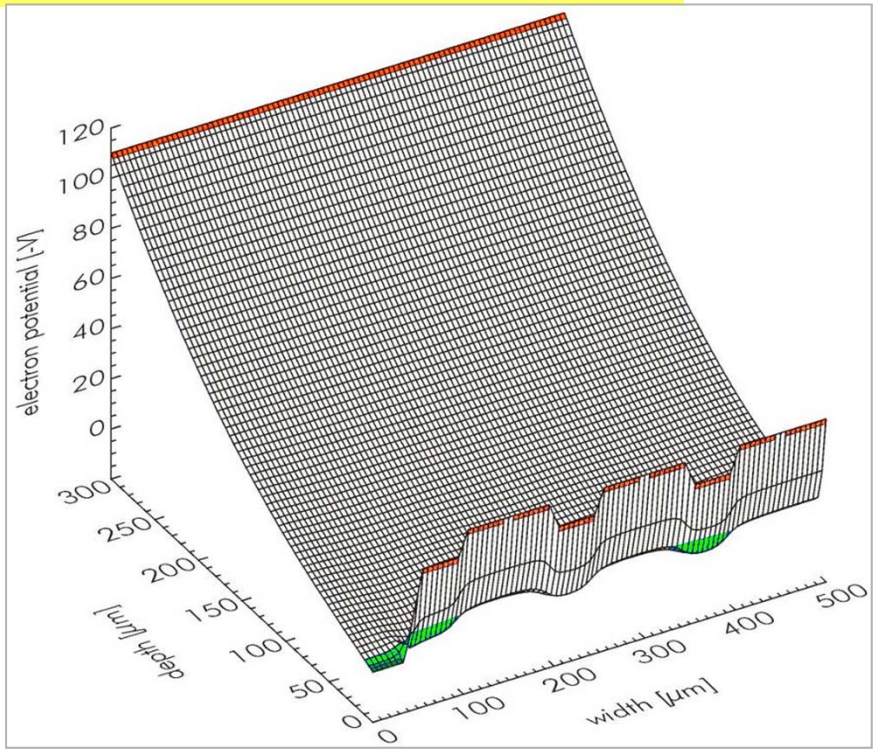
Controlled-drift detector

DePMOS



Fully Depleted pn-CCD (eg EPIC on XMM-N, CAMP,...)





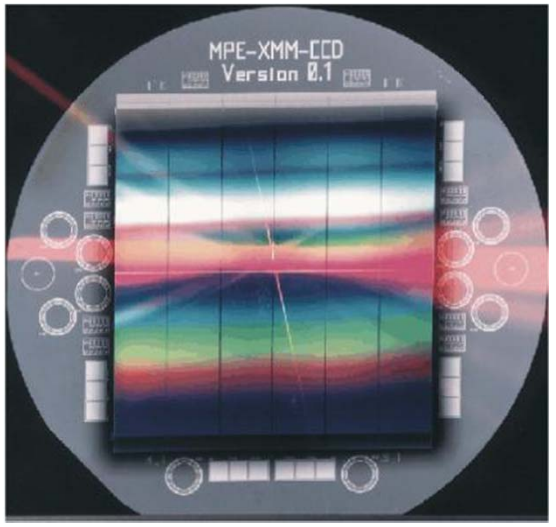
- charge from entire thickness collected and stored in potential trough (below Φ_2)
- by modulating potentials Φ_i → transfer charges until they reach read-out electrode(s)
- channel stops prevent that charges spill to neigbouring rows (eg from n → n±1)

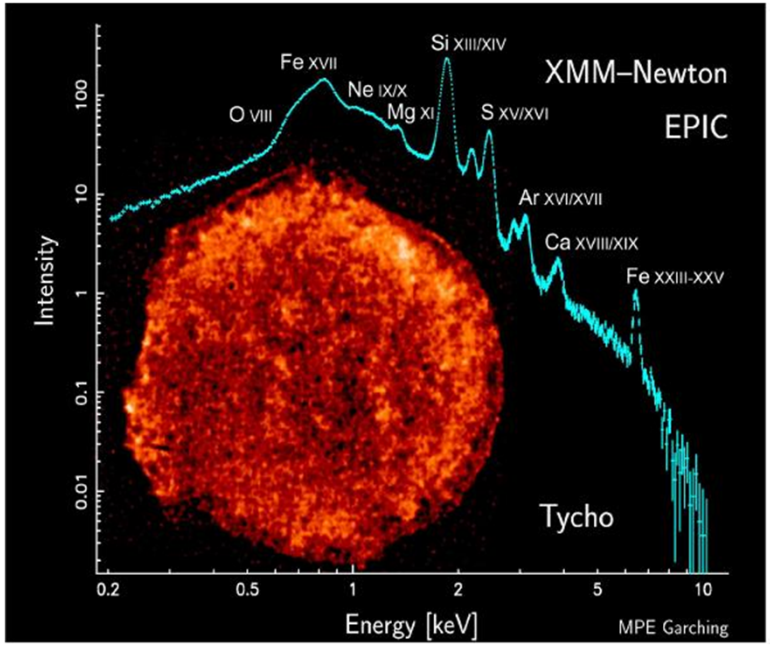
→ high quantum efficiency for X-rays due to full depletion (CMOS CCDs ~ 20 μm thick !)
→ backside illumination allows for thin entrance window (min. detectable X-ray energy !)
→ high transfer efficiency (uniform response)
→ pixel size down to ~30 μm
→ good radiation hardness because of pn junctions (no potential steering through oxide)

pn CCDs in Heaven

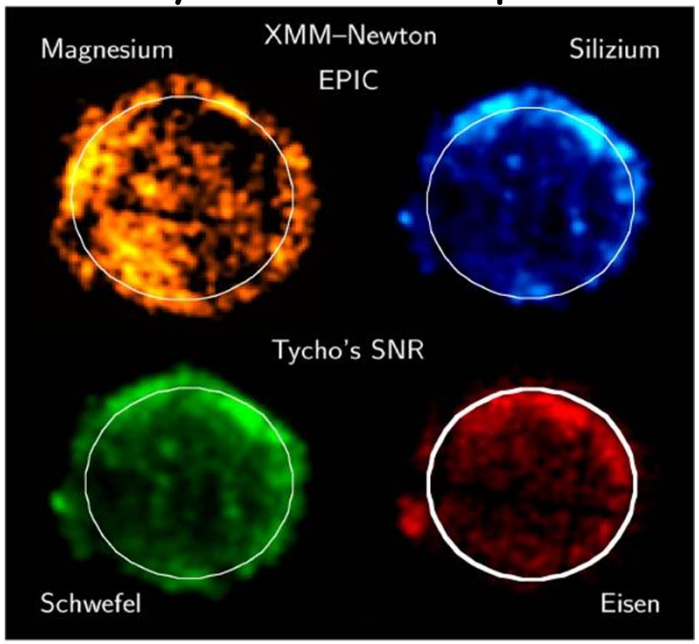
XMM-Newton satellite

pn-CCD





elemental analysis of TYCHO supernova remnant:



L. Strüder, IEEE-NSS 2004

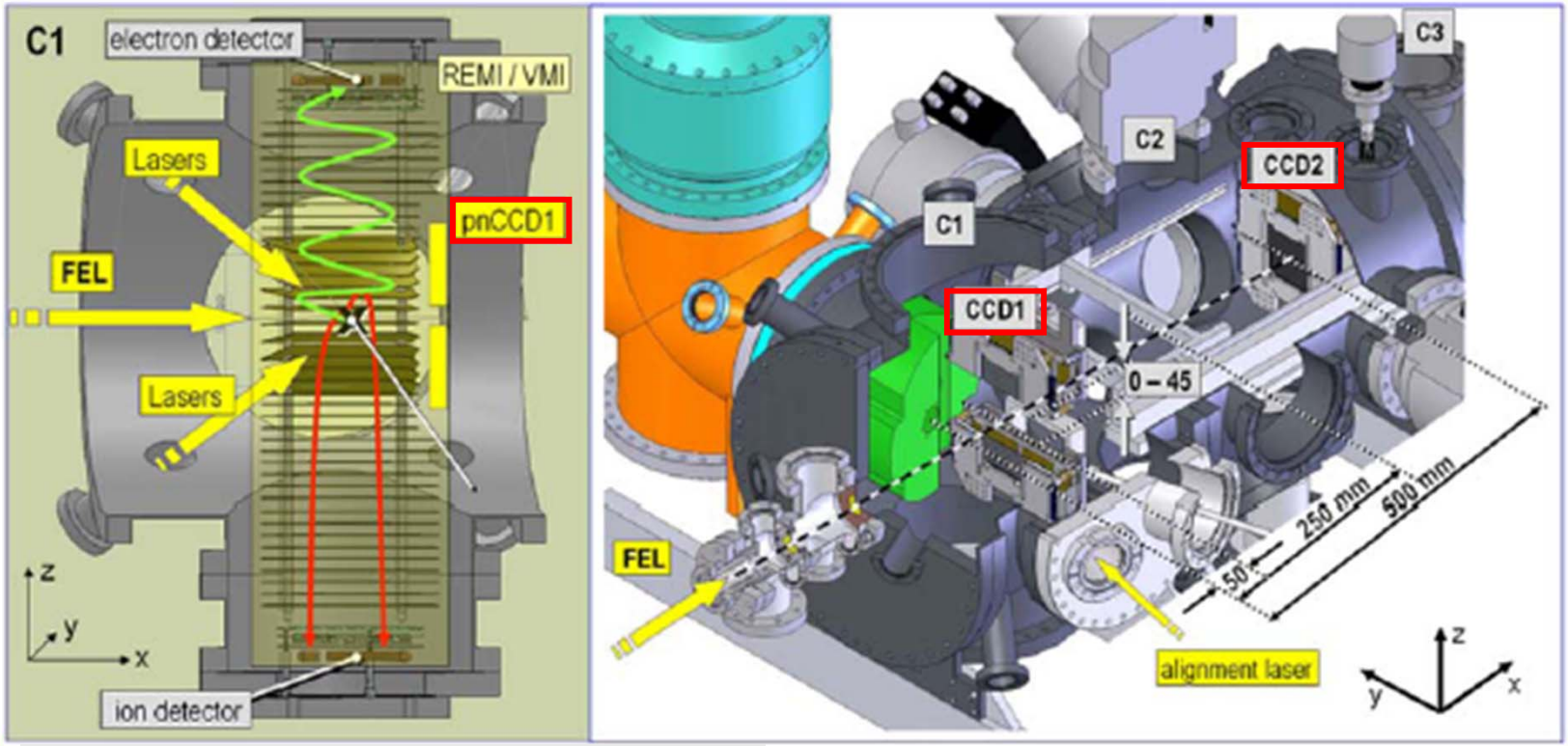
Detectors at the LCLS and other FELs

Experiments at FELs → unprecedented requirements for detectors:

- **energy resolution and dynamic range (0 →10^5 photons)**
- **segmentation and readout-speed**
- **charge densities and radiation dose (1 GGy @ EXFEL)**

Beautiful instruments existing + under developments → **iWoRID13**

Example for a running detector: CAMP (CFEL ASG MultiPurpose) detector



Femtosecond X-ray Protein Nanocrystallography

Example: CAMP@LCLS

- Most macromolecules cannot be grown to crystals of suf-ficent size for conventional crystallography*)
- X-ray dose required to study crystals will destroy them
- can fs pulses at FELs pro-duce diffraction pattern before damage occurred?
- experiment with CAMP at LCLS: 10^{12} 1.8keV γ/pulse of 10, 70 and 200 ns, focussed to 7µm (FWHM) → 70 MJ !

record 3M diffraction patterns of 0.2-2µm nanocrystals of photosystem I (structure known)

*) so far only 300 unique structures of membrane proteins deciphered !

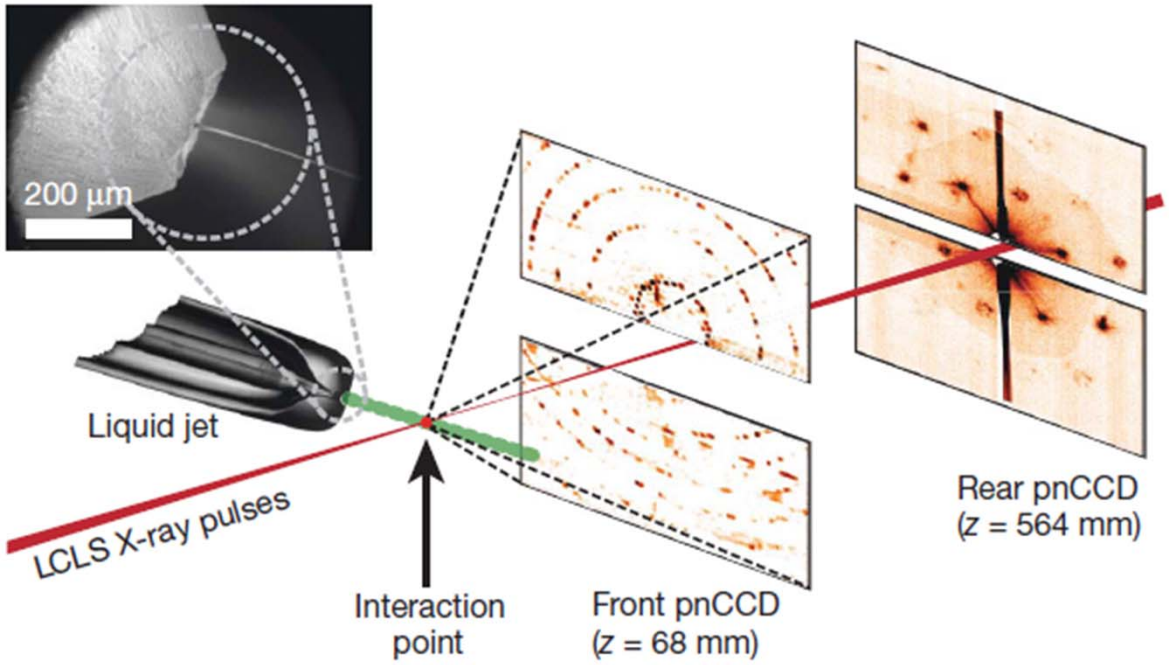
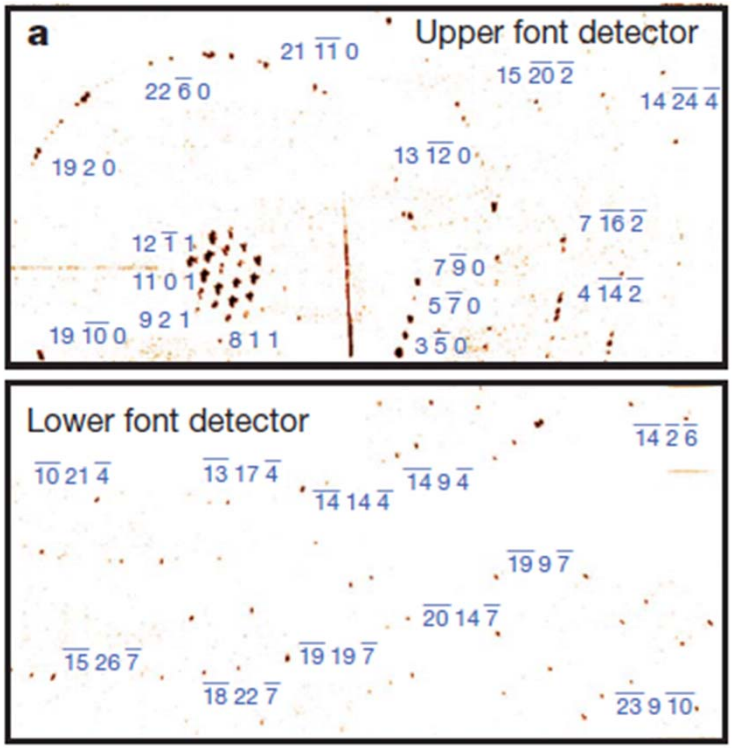


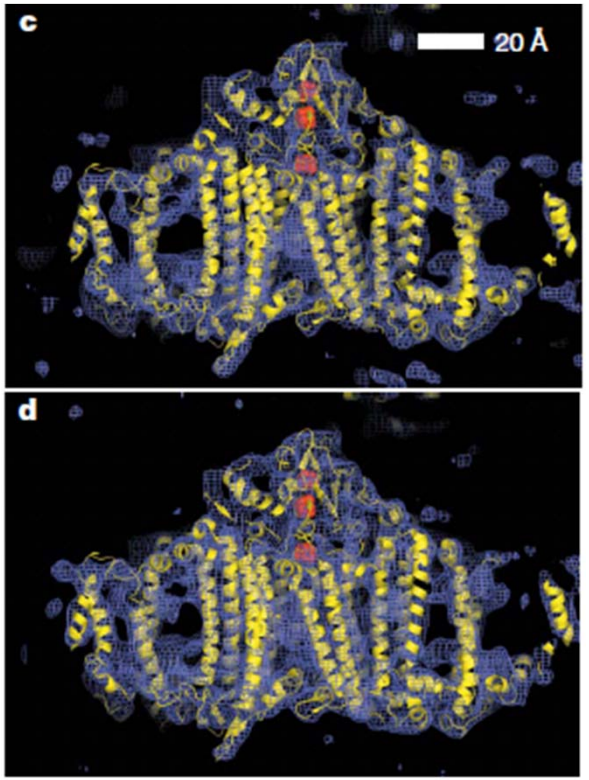
Figure 1 | Femtosecond nanocrystallography. Nanocrystals flow in their buffer solution in a gas-focused, 4-µm-diameter jet at a velocity of 10 m s^{-1} perpendicular to the pulsed X-ray FEL beam that is focused on the jet. Inset, environmental scanning electron micrograph of the nozzle, flowing jet and focusing gas[30]. Two pairs of high-frame-rate pnCCD detectors[12] record low- and high-angle diffraction from single X-ray FEL pulses, at the FEL repetition rate of 30 Hz. Crystals arrive at random times and orientations in the beam, and the probability of hitting one is proportional to the crystal concentration.

H.Chapman et al., Nature 470(2011)73

Femtosecond X-ray Protein Nanocrystallography



Diffraction pattern of single 70 fs pulse



Structure (c) 70 fs pulse; (d) conventional method truncated to 8.5 Å resolution

Single shot femtosecond nanocrystallography demonstrated !

→ excellent Si detectors were necessary for this success

→ further developments are required and under way to meet the challenges of the new X-ray sources – one of the main themes of IWORID13

Outlook and Summary

Looking back on > ½ a century of development of solid state sensor and detector systems:

- an exciting story of fascinating developments
- solid state detectors enabled important discoveries + precision measurements
- the developments have major impact on industry and science outside of physics
- frequently there has been amazingly little exchange between groups
- the close collaboration between academia and industry has been important

Looking forward:

- rapidly developing technologies bring new opportunities – they will help solving the many challenges posed by the new science ideas and the new experimental facilities, like Free-Electron Lasers, the High-Luminosity LHC, the International Linear Collider, and many more
- I also hope that there will also be completely new ideas, like in the past the CCD, the concept of sideway depletion, the DepFET and more

My thanks to:

- the many students + colleagues with whom I had (and have) the privilege to collaborate with
- the colleagues which provided me with information for this talk, in particular to H.Graafsma and S.Gruner